



Science and
Technology
Facilities Council

Characterisation of Redlen High-Flux CdZnTe at $>10^6$ ph s⁻¹ mm⁻² using

HEXITEC_{MHz}

Ben Cline^{a,1}, D. Banks^a, S. Bell^a, I. Church^a, A. Davis^a, T. Gardiner^a, J. Harris^a,
M. Hart^a, L. Jones^a, T. Nicholls^a, J. Nobes^a, S. Pradeep^a, M. Roberts^a, D. Sole^a,
M.C. Veale^a, M.D. Wilson^a, V. Dhamgaye^b, O. Fox^b, K. Sawhney^b.

^aUKRI STFC Rutherford Appleton Laboratory

^bDiamond Light Source

Email: ben.cline@stfc.ac.uk

02/07/2024

Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

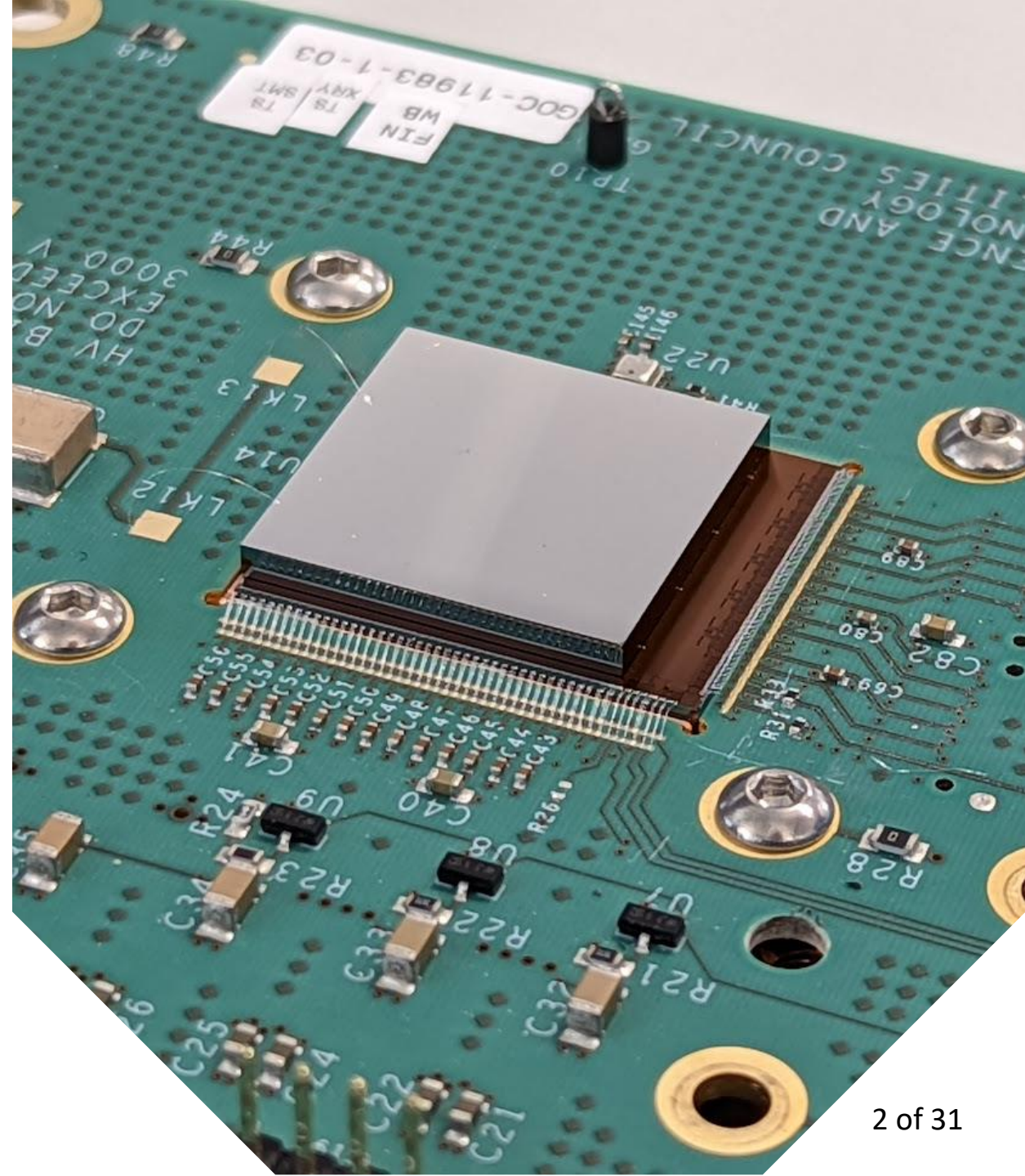
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

5 Next Steps

Future Work planned



Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

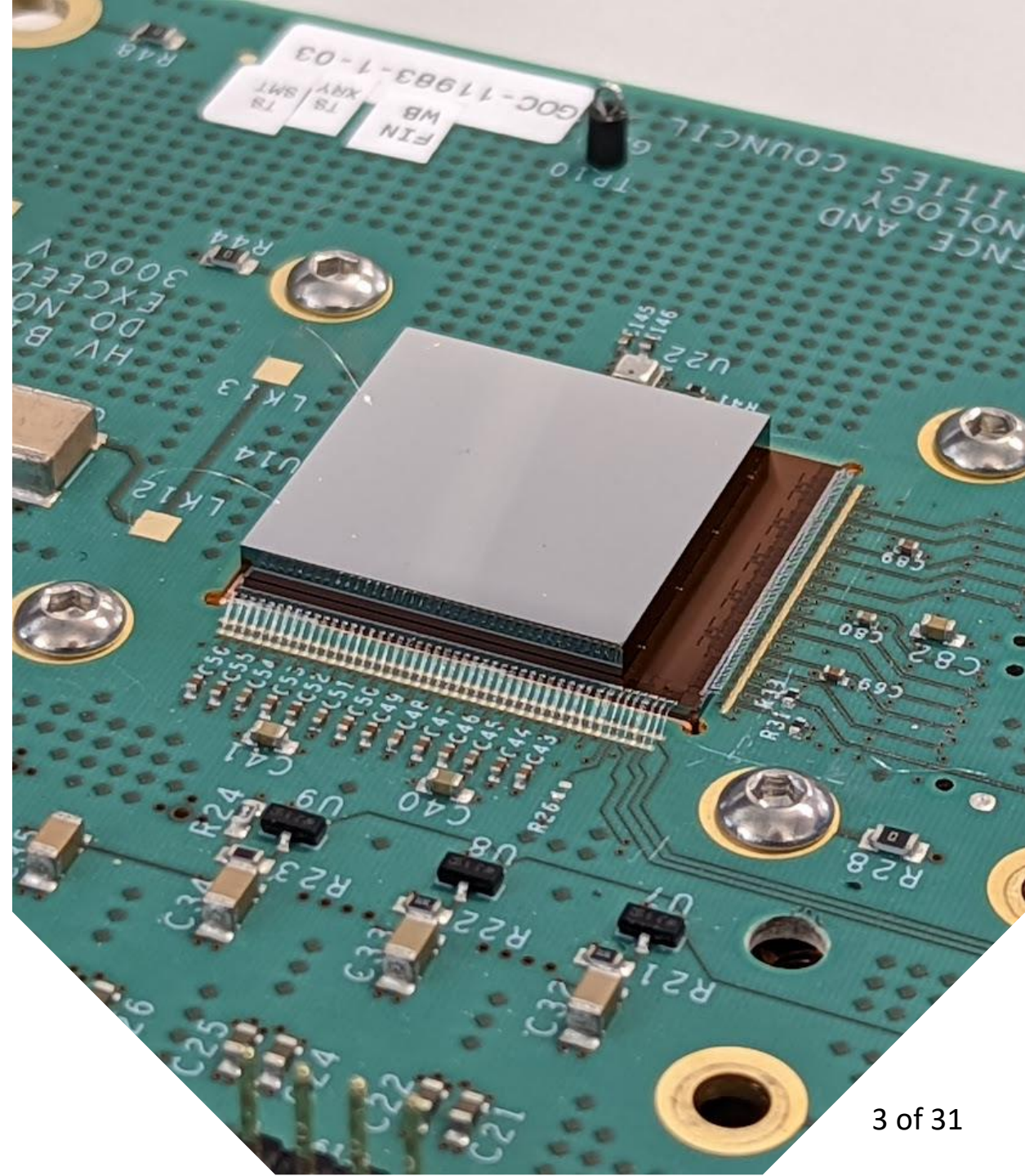
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

5 Next Steps

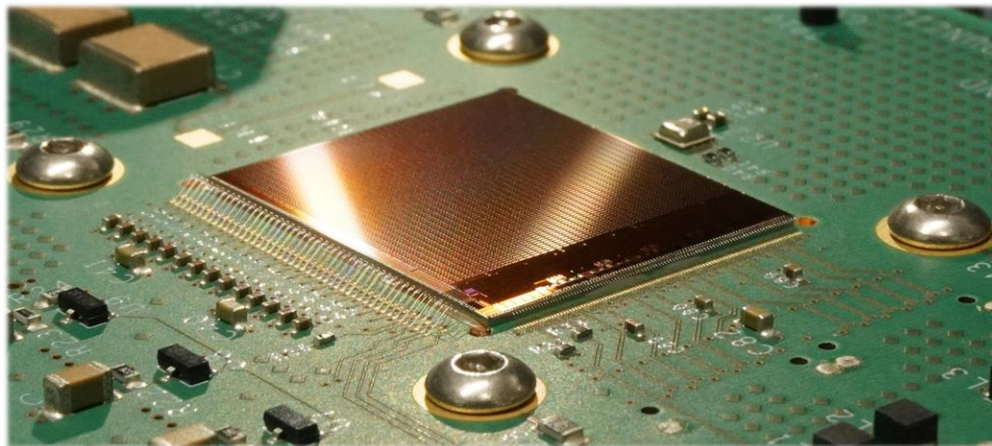
Future Work planned



HEXITEC_{MHz}

New fully spectroscopic X-ray imaging detector:

- **1 MHz continuous frame rate**
 - Spectroscopic X-ray fluxes of $>10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$
 - Facilitated by:
 - **Integrating Front End** with $<70 \text{ e}^- \text{ ENC}$
 - **12-bit on-chip digitisation** in TDCs
 - **20 × 4.1 Gbps serialisers** for data output
- 80 × 80 pixels on a 250 μm pitch



HEXITEC_{MHz} ASIC



Science and
Technology
Facilities Council

Comparison of HEXITEC and HEXITEC_{MHz} specifications

Parameter	HEXITEC	HEXITEC _{MHz}
Pixel Pitch (μm)	250	250
Array Size	80 × 80	80 × 80
Max Frame Rate (kHz)	9.81	1000
Max Spectroscopic Flux (ph s ⁻¹ mm ⁻²)	~10 ⁴	>10⁶
Digitisation	Off-chip	On-chip
Detector Type	Track + Hold	Integrating
Gain Stages (keV in CZT)	200	100
	600	200
		300
FWHM@100keV (keV in CZT)	<1	<1
Power Consumption (W)	1.5	15

HEXITEC_{MHz}

New fully spectroscopic

- 1 MHz continuous
- Spectroscopic
- Facilitated
 - Integrating
 - 12-bit
 - 20 × 4
- 80 × 80 pixels of



HEXITEC_{MHz} ASIC

IOPscience Journals Books Publishing Support Login

Journal of Instrumentation

PAPER • OPEN ACCESS

Spectroscopic X-ray imaging at MHz frame rates — the HEXITEC_{MHz} ASIC

L. Jones^{2,1}, S. Bell¹, B. Cline¹, T. Gardiner¹, M. Hart¹, M. Prydderch¹, P. Seller¹, M. Veale¹ and M. Wilson¹

Published 11 October 2022 • © 2022 The Author(s). Published by IOP Publishing Ltd on behalf of Sissa Medialab.

[Journal of Instrumentation, Volume 17, October 2022](#)

Citation L. Jones *et al* 2022 *JINST* 17 C10012

DOI: 10.1088/1748-0221/17/10/C10012

Specifications

	HEXITEC _{MHz}
	250
	80 × 80
	1000
	>10⁶
	On-chip
	Integrating
	100
	200
	300
FWHM@100keV (keV in CZT)	<1
Power Consumption (W)	1.5

Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

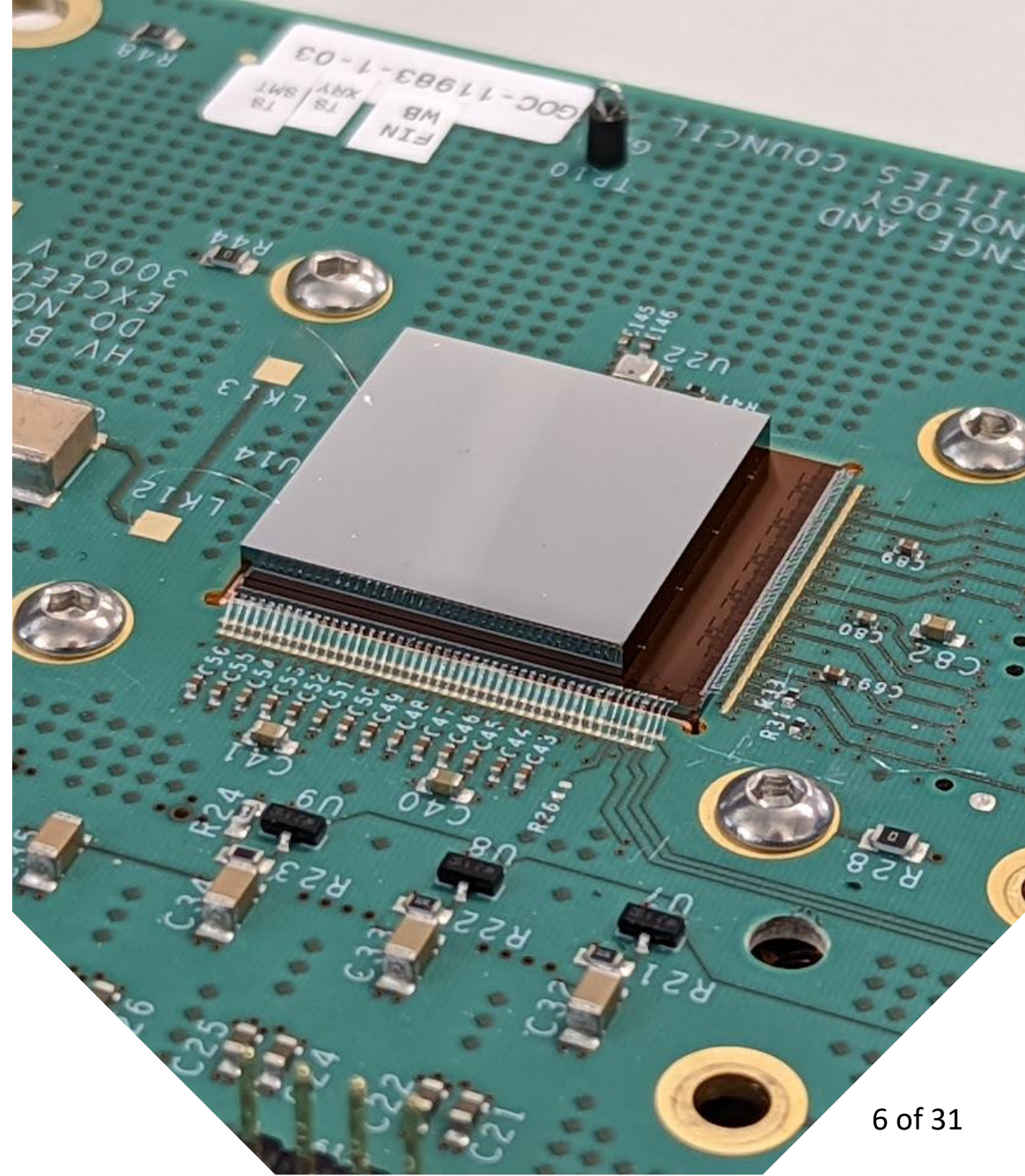
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

5 Next Steps

Future Work planned

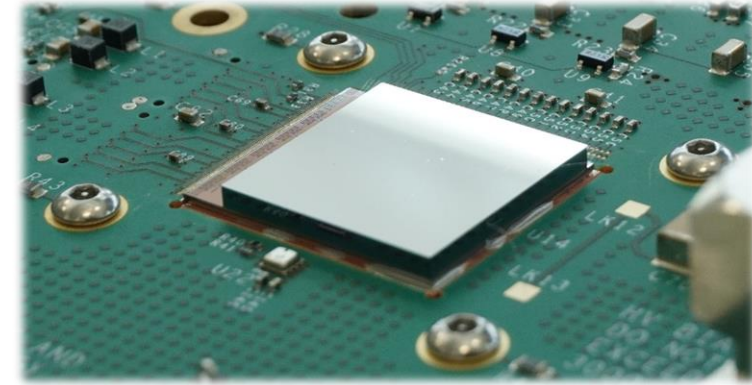


Redlen High-Flux Capable CdZnTe

- **Spectroscopic-grade CdZnTe.**
 - Optimised e⁻ transport properties and spectral resolution
 - **Poor h⁺ lifetime and mobility ($\tau_h \approx 0.2 \mu\text{s}$, $\mu_h \approx 0.1\mu_e$)**
 - **h⁺ trapping and polarization $>10^6 \text{ ph}^{-1} \text{ s}^{-1} \text{ mm}^{-2}$**
- **Medical and Security CT applications** require:
 - $>10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ X-ray fluxes
- **High-Flux Capable CdZnTe (HF-CZT)**
 - Introduced in 2017 by Redlen
 - $\sim 10\times$ increase in τ_h – allows operation $<10^9 \text{ ph s}^{-1} \text{ mm}^{-2}$

HEXITEC_{MHz} HF-CZT detectors

- 2 mm thick sensors - two Pt electrodes, 25 μm inter-pixel gap
- ASIC hybridisation by UKRI STFC Interconnect - cured at 150°C



HF-CZT sensor hybridised to HEXITEC_{MHz} ASIC

Results from Thomas et al., 2017 [1]

Table 1. A summary of the measured charge transport properties of three “high-flux” Redlen CdZnTe detectors [14, 16].

	$\mu_e \tau_e$ ($\times 10^{-4} \text{ cm}^2 \text{ V}^{-1}$)	μ_e ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	τ_e ($\times 10^{-6} \text{ s}$)	$\mu_h \tau_h$ ($\times 10^{-4} \text{ cm}^2 \text{ V}^{-1}$)	μ_h ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	τ_h ($\times 10^{-6} \text{ s}$)
High Flux CdZnTe	11 ± 6	940 ± 190	1.2 ± 0.8	2.9 ± 1.4	114 ± 22	2.5 ± 1.4
Standard CdZnTe	100	1100	11	0.2	88	0.2

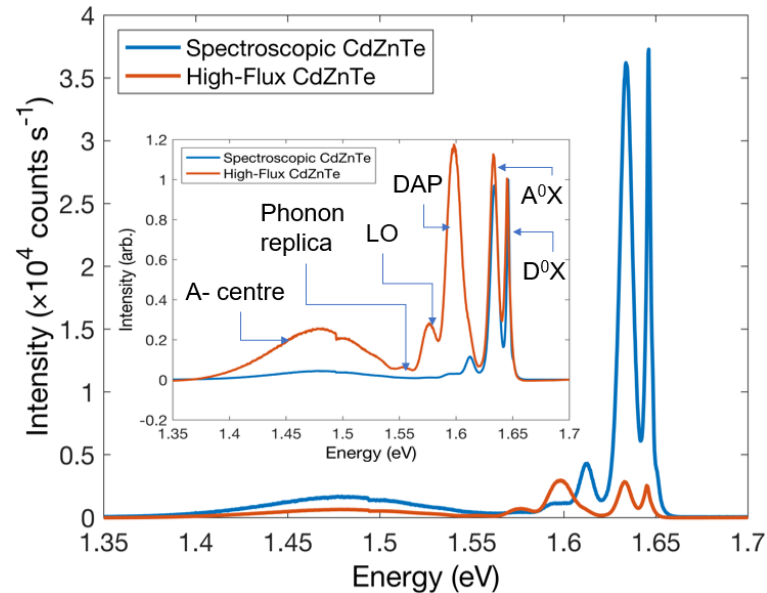
Redlen High-Flux Capable CdZnTe

- Spectroscopic-grade
 - Optimised e
 - **Poor h⁺ life**
 - **h⁺ trap**
- Medical and Sec
 - >10⁶ ph s⁻¹
- High-Flux Capab
 - Introduced
 - ~10× increa

Charge Transport Properties and Linearity of HF-CdZnTe Material

M. Bishop^{1,2*}, B. D. Cline¹, E. Gimenez³, F. K. Dejene², I. Braddock¹, J. Matheson³, M. Larkin¹, M. Wilson¹, M. Veale¹, O. Fox³, S. Bugby², S. Scully³, S. Knowles¹, S. Zanettini⁴, V. Dhamgaye³

**POSTER ON DISPLAY THIS WEEK
- SEE MAX BISHOP**



4 K low temperature photoluminescence spectrum of HF-CdZnTe and spectroscopic CdZnTe. Taken with 400mA excitation led intensity, integration time has been converted into counts per second. (Insert) Spectrum normalised to D⁰X peak. Notch at 1.48 eV is due to image stitching error.

EC_{MHz} ASIC

[1]

properties of three “high-flux” Redlen CdZnTe

$\mu_h \tau_h$ ($\times 10^{-4} \text{ cm}^2 \text{ V}^{-1}$)	μ_h ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	τ_h ($\times 10^{-6} \text{ s}$)
2.9 ± 1.4	114 ± 22	2.5 ± 1.4
0.2	88	0.2

HEXITEC_{MHz} HF-Ca

- 2 mm thick sense
- ASIC hybridisation by UKRI STFC Interconnect - cured at 150°C



Science and
Technology
Facilities Council

Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

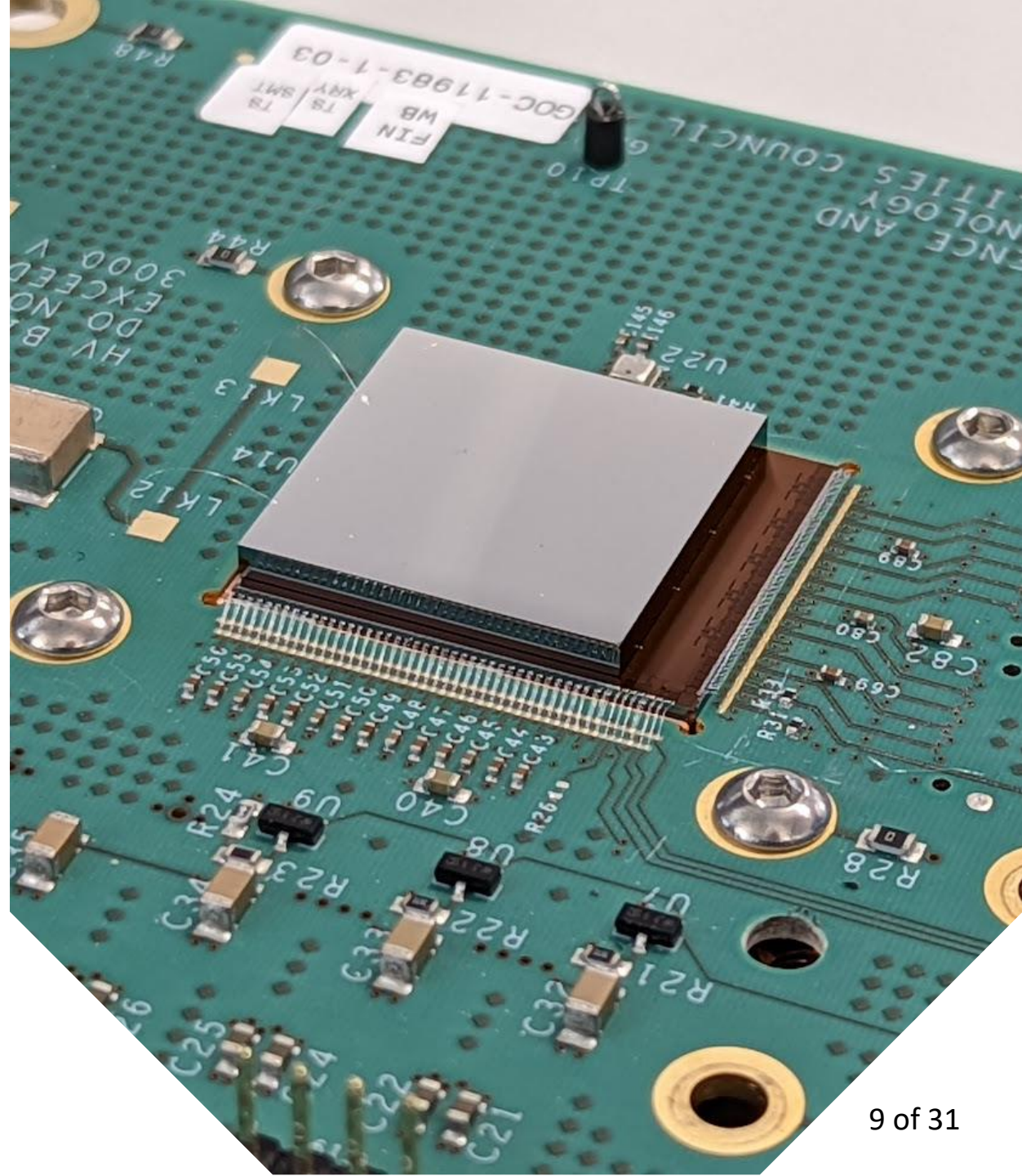
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

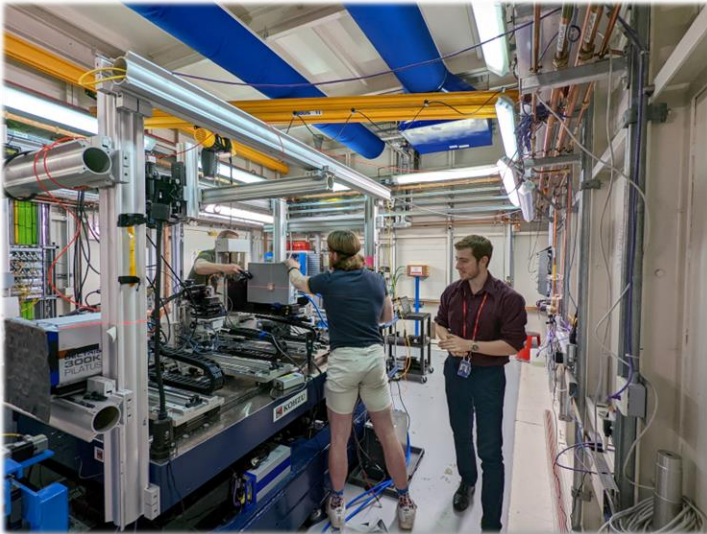
5 Next Steps

Future Work planned

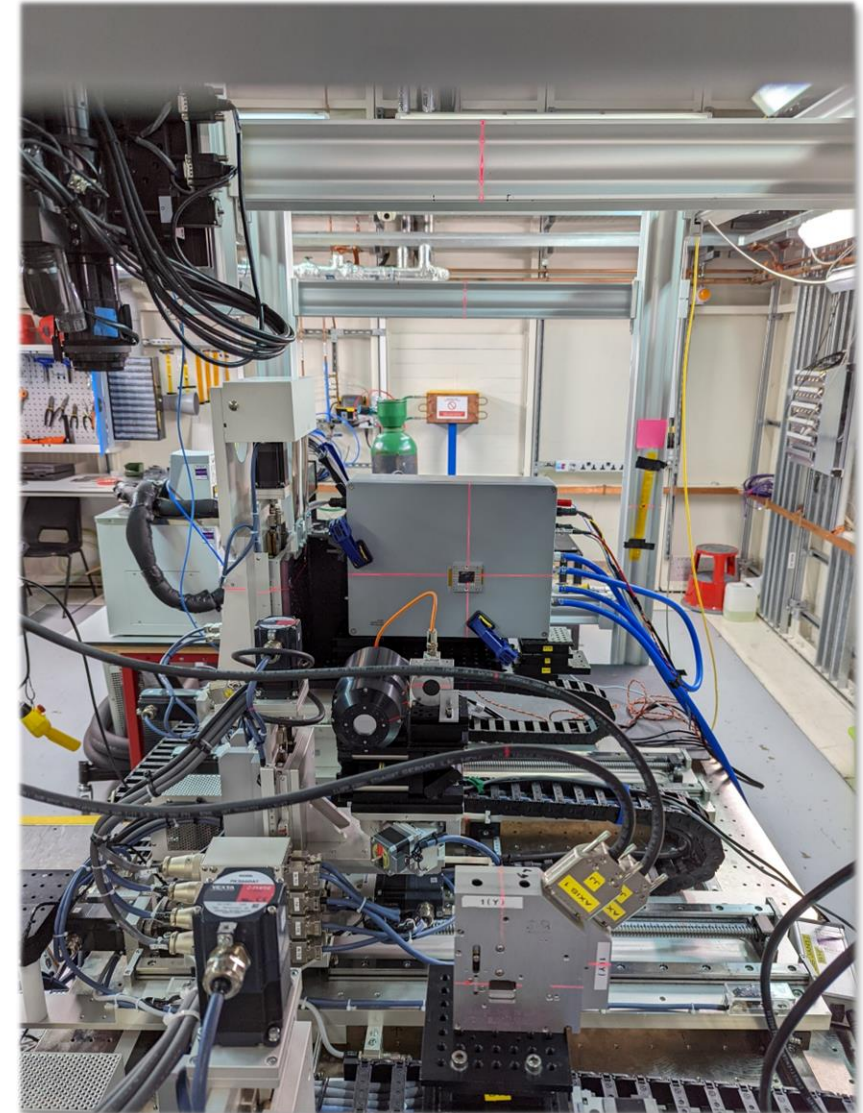


Experimentation at diamond

- **B16 Beamline: August 2022, December 2022, December 2023**
 - Monochromatic X-rays: 10 – 20 keV
 - Photon fluxes: $10^5 - 10^8 \text{ ph s}^{-1} \text{ mm}^{-2}$
 - 1 MHz data stream on one/four fast-data channels
 - Tested **HF-CZT (2 mm)**, **p-type Si (300 μm)**, **GaAs (500 μm)** devices
- Beamline scientists: Vishal Dhamgaye, Oliver Fox, Kawal Sawhney



B16 setup photos



- B16 Beamline
 - Monorail
 - Photodiode
 - 1 MHz
 - Teste
- Beamline s



IOPscience Journals Books Publishing Support Login

Journal of Instrumentation

PAPER • OPEN ACCESS

Preliminary characterisation of the HEXITEC_{MHZ} spectroscopic X-ray imaging detector

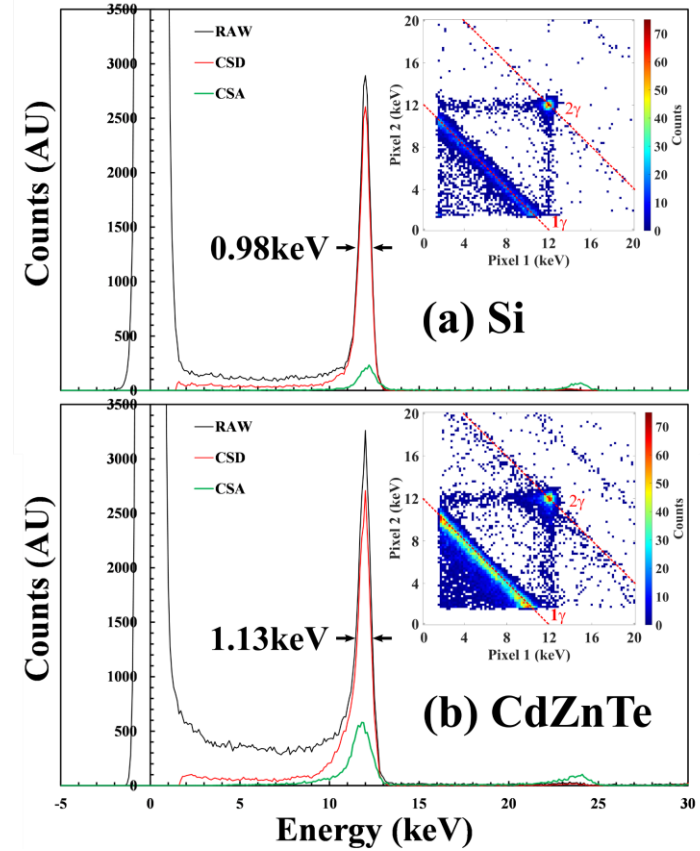
M.C. Veale¹, S. Bell¹, B.D. Cline¹, I. Church¹, S. Cross¹, C. Day¹, M. French¹, T. Gardiner¹, N. Ghorbanian¹, M.D. Hart¹ [+ Show full author list](#)

Published 28 July 2023 • © 2023 The Author(s)

[Journal of Instrumentation, Volume 18, July 2023](#)

Citation M.C. Veale *et al* 2023 *JINST* 18 P07048

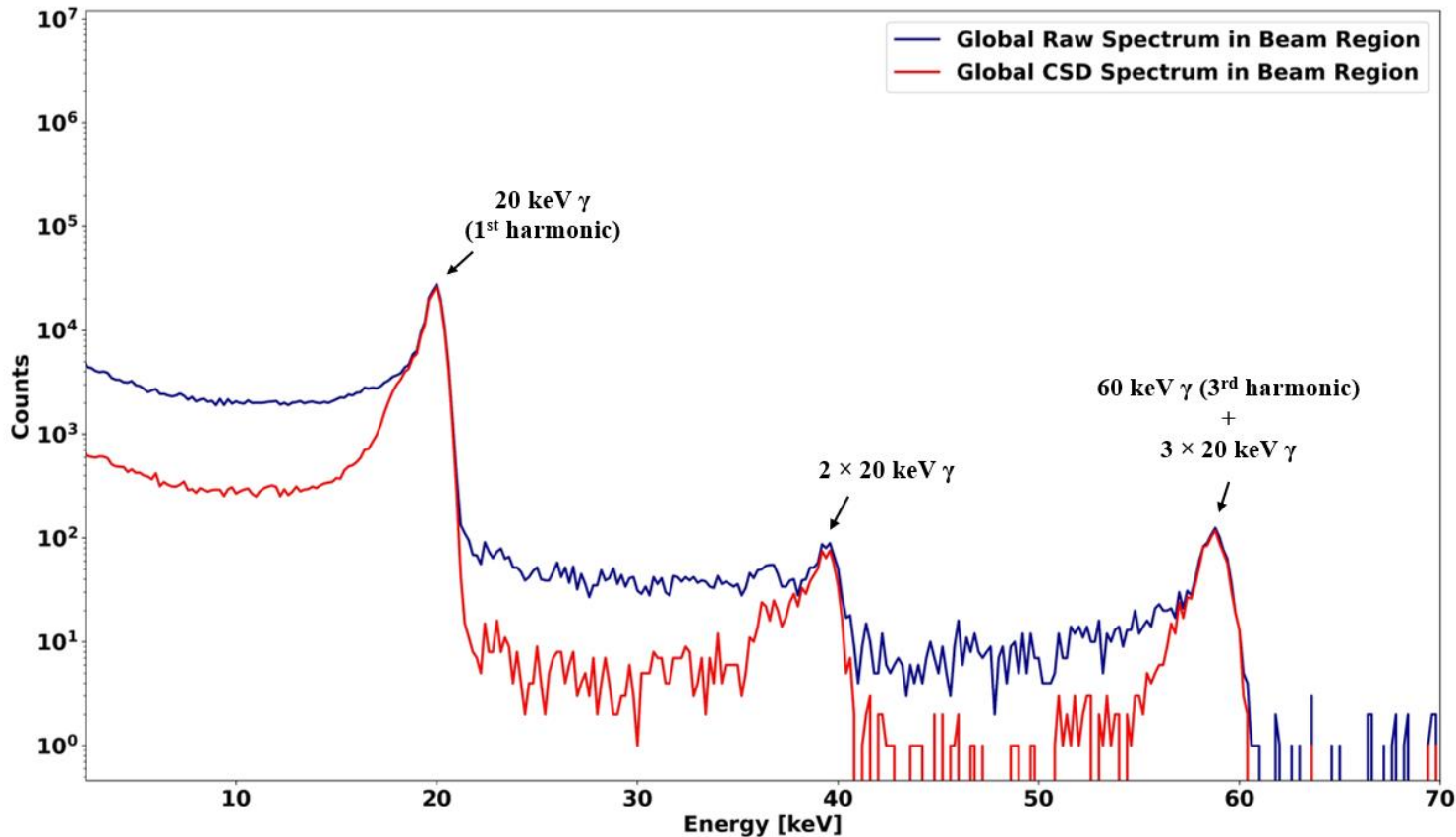
DOI: 10.1088/1748-0221/18/07/P07048



HF-CZT Spectroscopic Imaging Characterisation

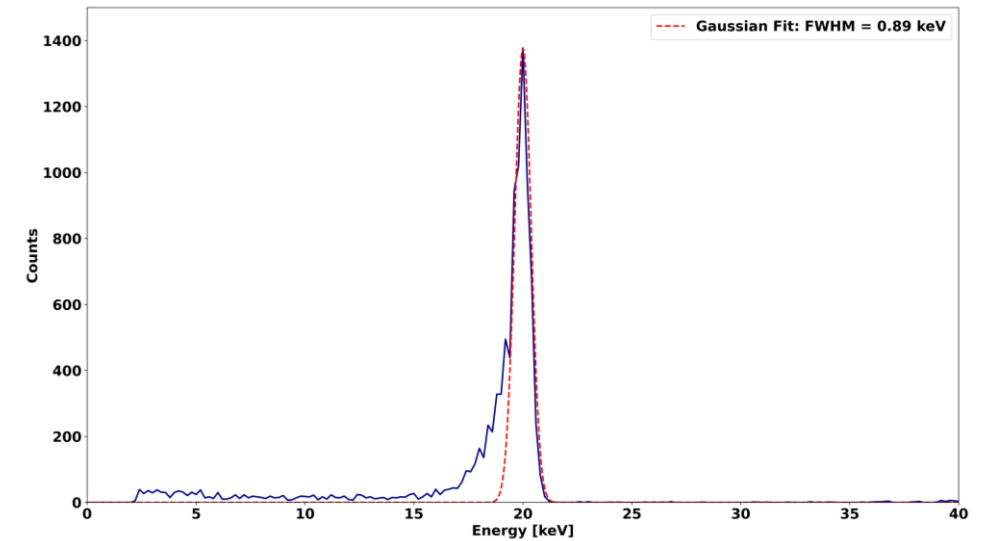
Summary of 20 keV spectroscopic results (HG = High gain etc.)

Energy (keV)	HG FWHM (keV)	MG FWHM (keV)	LG FWHM (keV)
20	0.85 ± 0.10	0.92 ± 0.11	1.13 ± 0.12

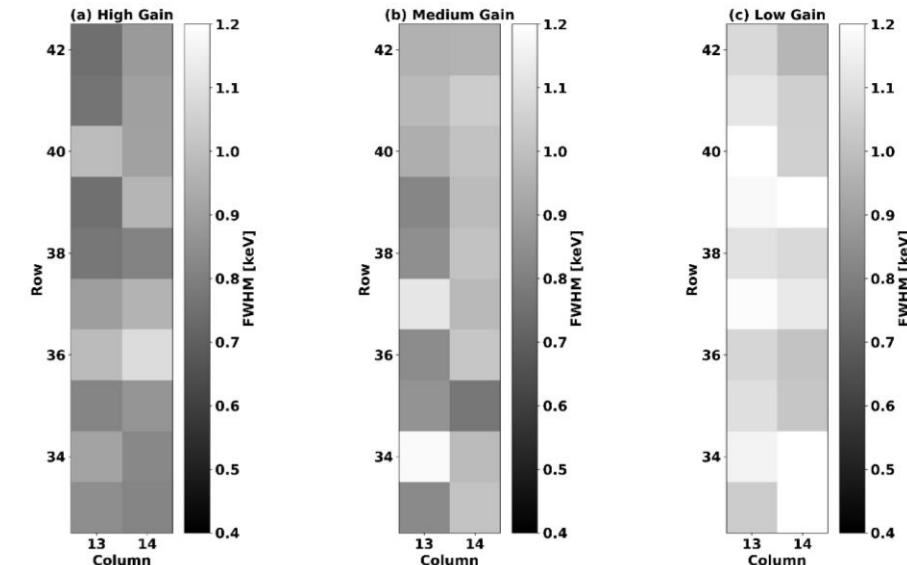


Science and
Technology
Facilities Council

Calibrated raw and CSD spectra of illuminated pixels in an 8 mm Al 20 keV high-gain dataset ($2.93 \times 10^5 \text{ ph s}^{-1} \text{ mm}^{-2}$) - 0.1 keV bin width

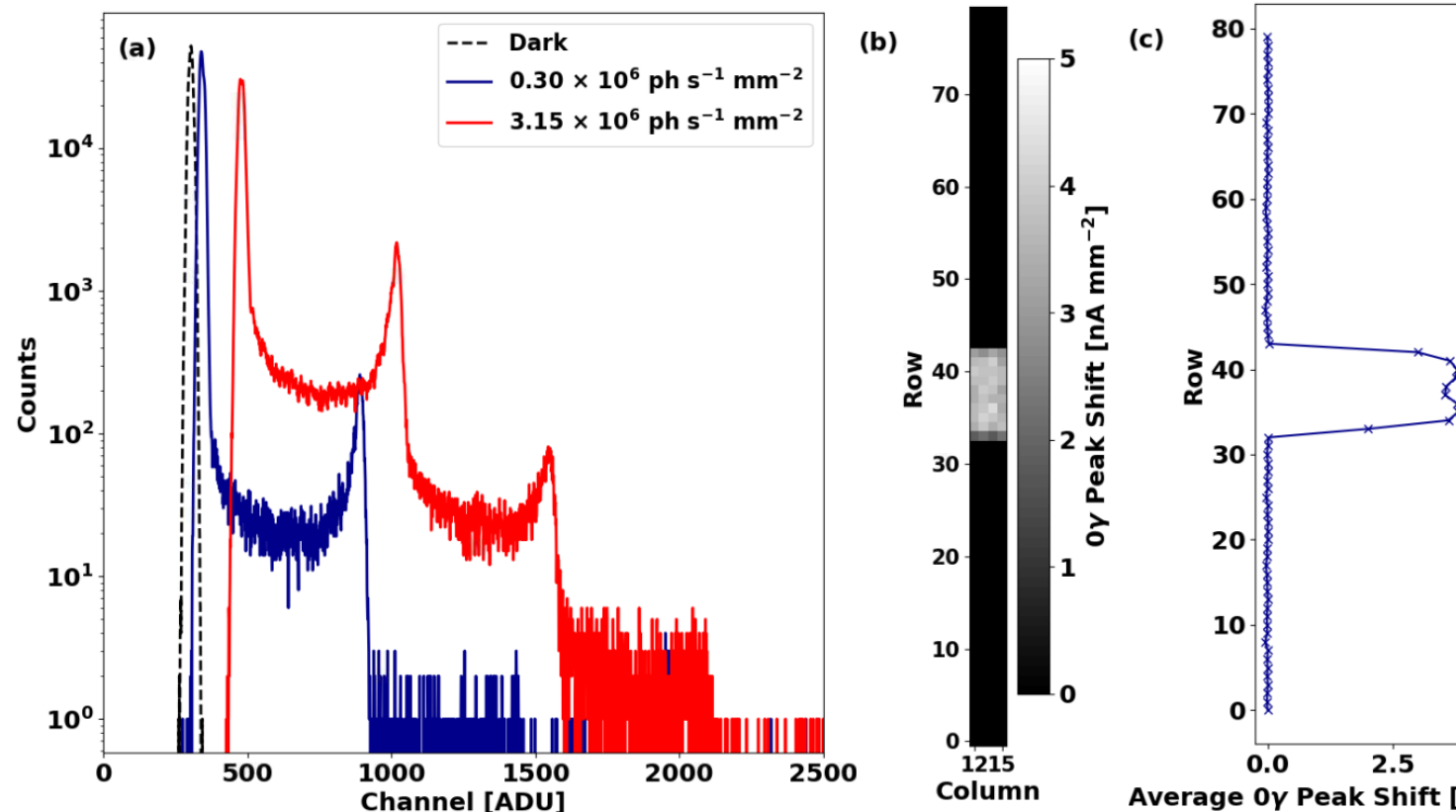


Pixel (13,37) high-gain CSD spectrum with Gaussian fit to the 20 keV photo peak - 0.2 keV bin width



20 keV FWHM distributions in the beam

'Excess Leakage Current Effect' Identification - Comparing HF-CZT data at two fluxes



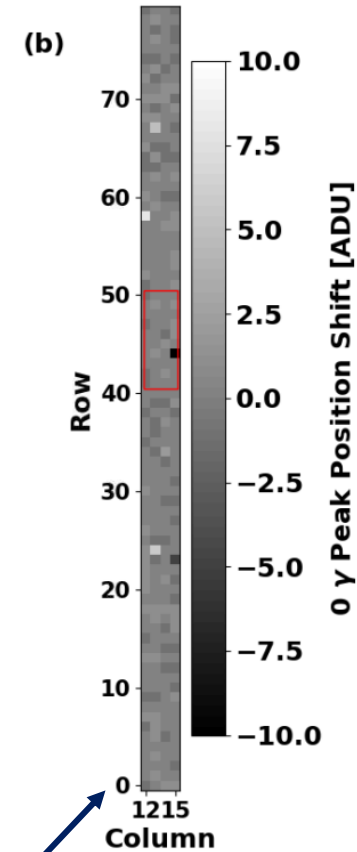
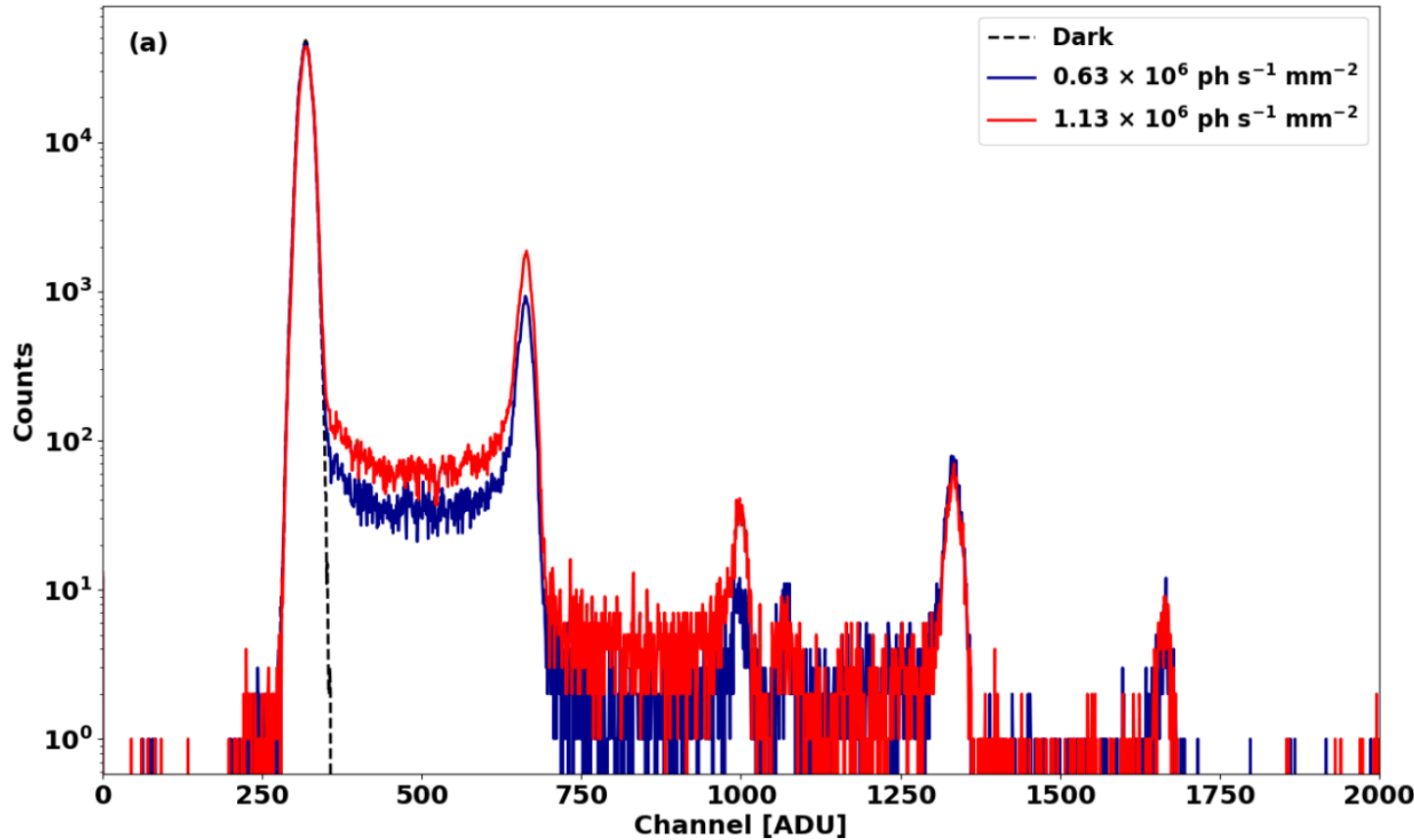
*Average results in beam**

Flux ($10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$)	Offset (ADU)	Offset (keV)	Offset (nA mm ⁻²)
0.30	36 ± 7	1.31 ± 0.25	0.80 ± 0.15
3.15	160 ± 28	5.91 ± 1.05	3.60 ± 0.64

20 keV high-gain results at $0.30 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ and $3.15 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$. (a) Pixel (13,37) raw spectra – 1 ADU bin width. (b) Map of $3.15 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ 0γ peak shifts. (c) Average $3.15 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ 0γ peak shift across each readout row

$$* \text{ Shift [A mm}^{-2}] = \frac{\text{Shift [ADU]} \times (\text{ADU} - \text{keV conversion factor})}{\text{Integration time} \times (\text{CZT pair conversion energy}) \times \text{Pixel area}}$$

'Excess Leakage Current Effect' Identification - Comparing p-type Si data at two fluxes



p-type Si FWHM results

Energy (keV)	HG FWHM (keV)	MG FWHM (keV)
10	0.66 ± 0.06	0.77 ± 0.10
15	0.68 ± 0.06	0.81 ± 0.10

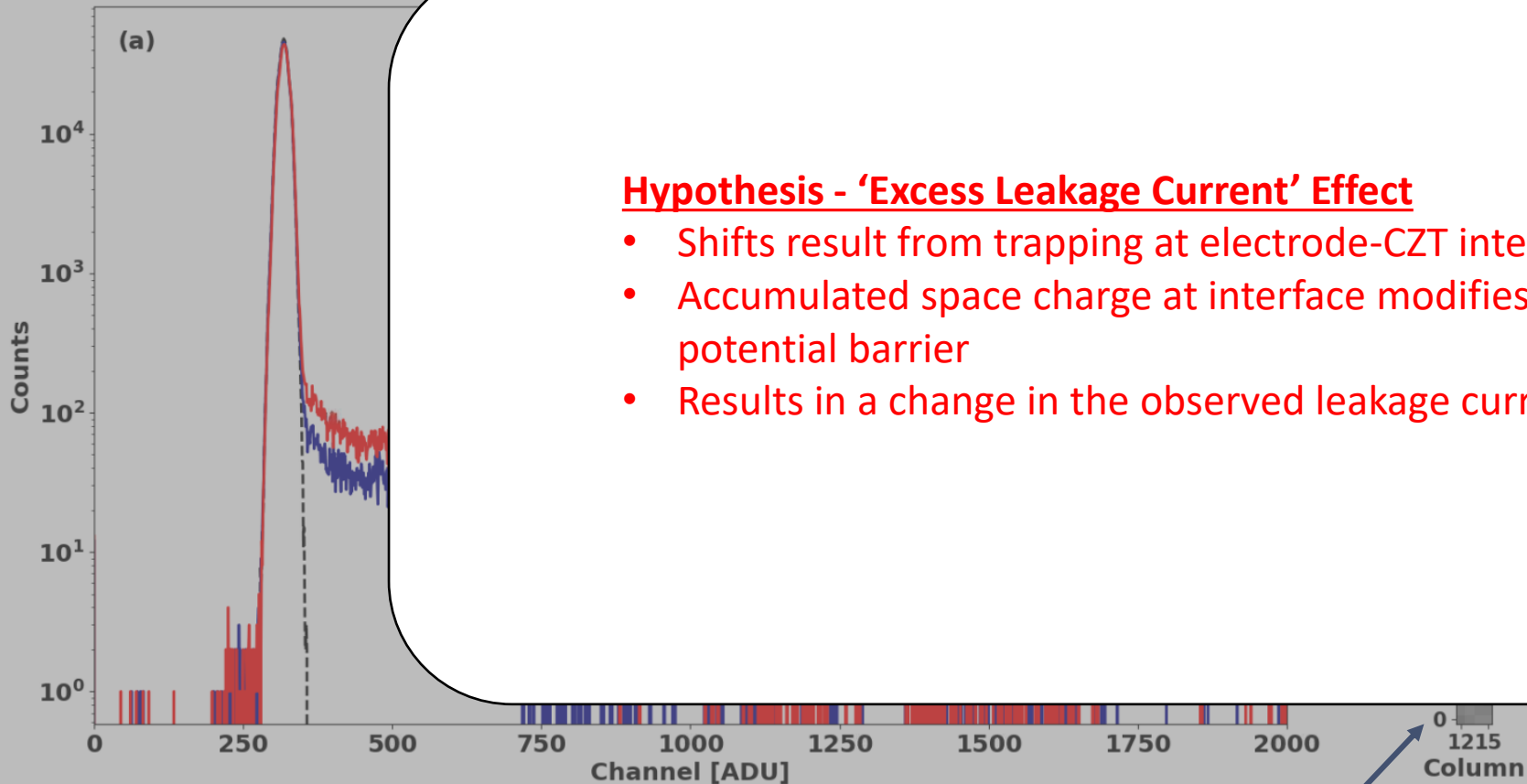
10 keV p-type Si high-gain results at $0.63 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ and $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$. (a) Pixel (15,44) raw spectra – 1 ADU bin width. (b) Map of $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ 0γ peak shifts. Beam position highlighted red

<3 ADU shifts result of minor ASIC power-supply fluctuations



Science and Technology Facilities Council

'Excess Leakage Current Effect' Identification - Comparing p-type Si data at two fluxes



Hypothesis - 'Excess Leakage Current' Effect

- Shifts result from trapping at electrode-CZT interface
- Accumulated space charge at interface modifies the potential barrier
- Results in a change in the observed leakage current

n-type Si FWHM results

HG FWHM (keV)	MG FWHM (keV)
0.66 ± 0.06	0.77 ± 0.10
0.68 ± 0.06	0.81 ± 0.10

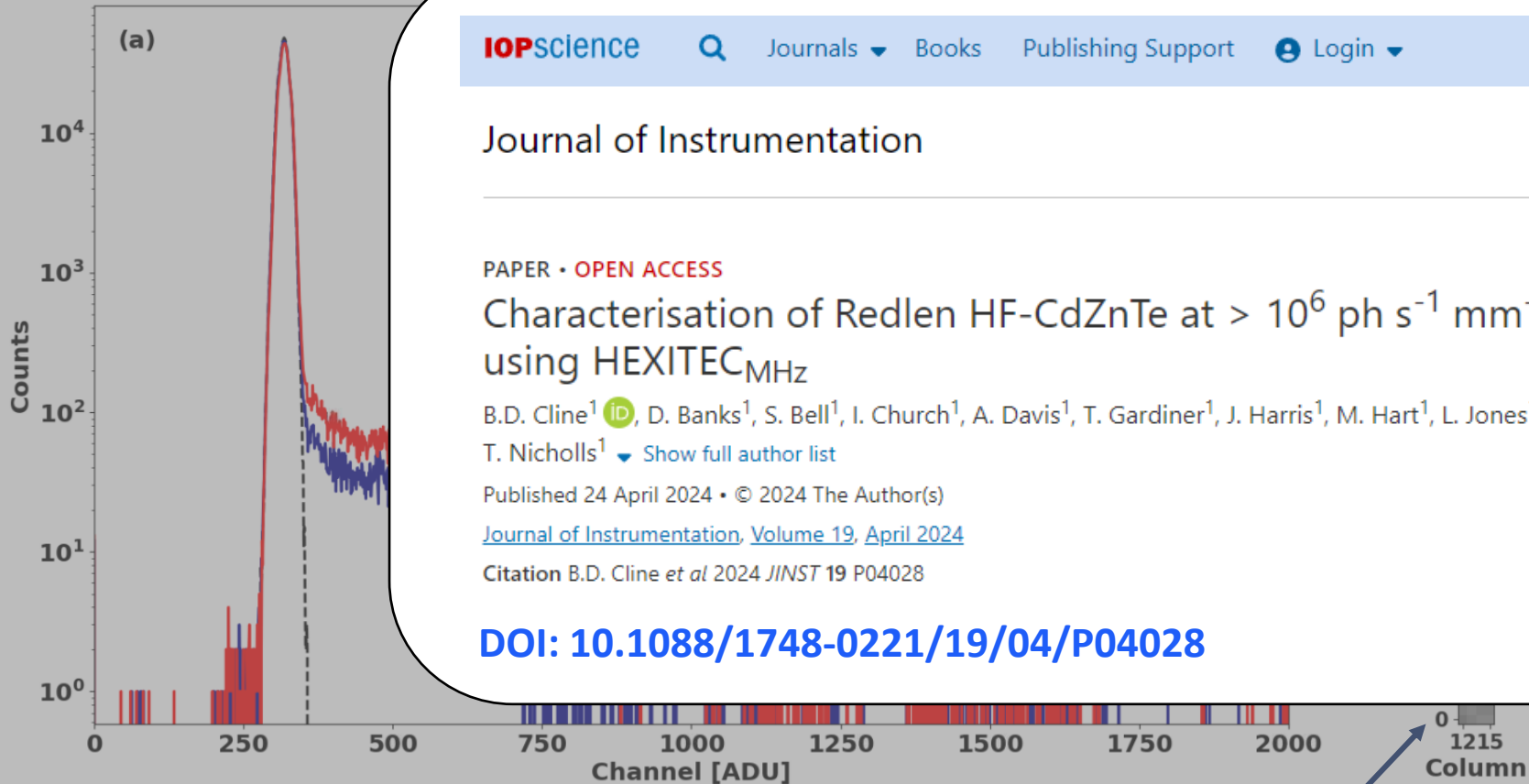
n-type Si high-gain results
 $10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ and $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$. (a) Pixel (15,44)
 extra - 1 ADU bin width. (b) $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2} 0\gamma$

peak shifts. Beam position highlighted red

<3 ADU shifts result of minor ASIC power-supply fluctuations



'Excess Leakage Current Effect' Identification - Comparing p-type Si data at two fluxes



IOPscience Journals Books Publishing Support Login

Journal of Instrumentation

PAPER • OPEN ACCESS

Characterisation of Redlen HF-CdZnTe at $> 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ using HEXITEC_{MHZ}

B.D. Cline¹, D. Banks¹, S. Bell¹, I. Church¹, A. Davis¹, T. Gardiner¹, J. Harris¹, M. Hart¹, L. Jones¹, T. Nicholls¹

Published 24 April 2024 • © 2024 The Author(s)

[Journal of Instrumentation, Volume 19, April 2024](#)

Citation B.D. Cline *et al* 2024 *JINST* 19 P04028

DOI: 10.1088/1748-0221/19/04/P04028

n-type Si FWHM results

HG FWHM (keV)	MG FWHM (keV)
0.66 ± 0.06	0.77 ± 0.10
0.68 ± 0.06	0.81 ± 0.10

n-type Si high-gain results
 $10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ and $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$. (a) Pixel (15,44)
 Ultra – 1 ADU bin width. (b) $1.13 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$ 0y

peak shifts. Beam position highlighted red

<3 ADU shifts result of minor ASIC power-supply fluctuations



Science and Technology Facilities Council

Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

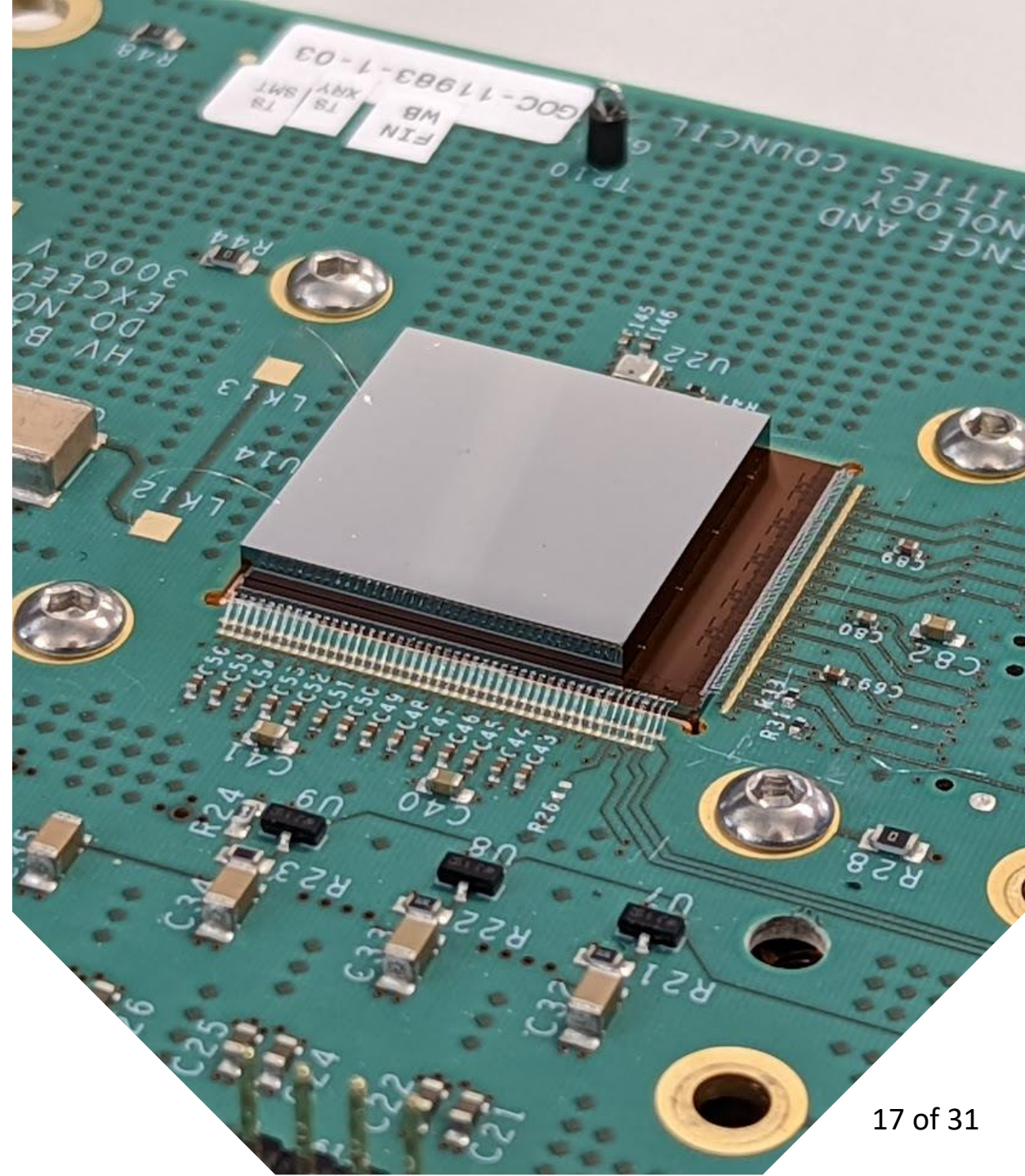
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

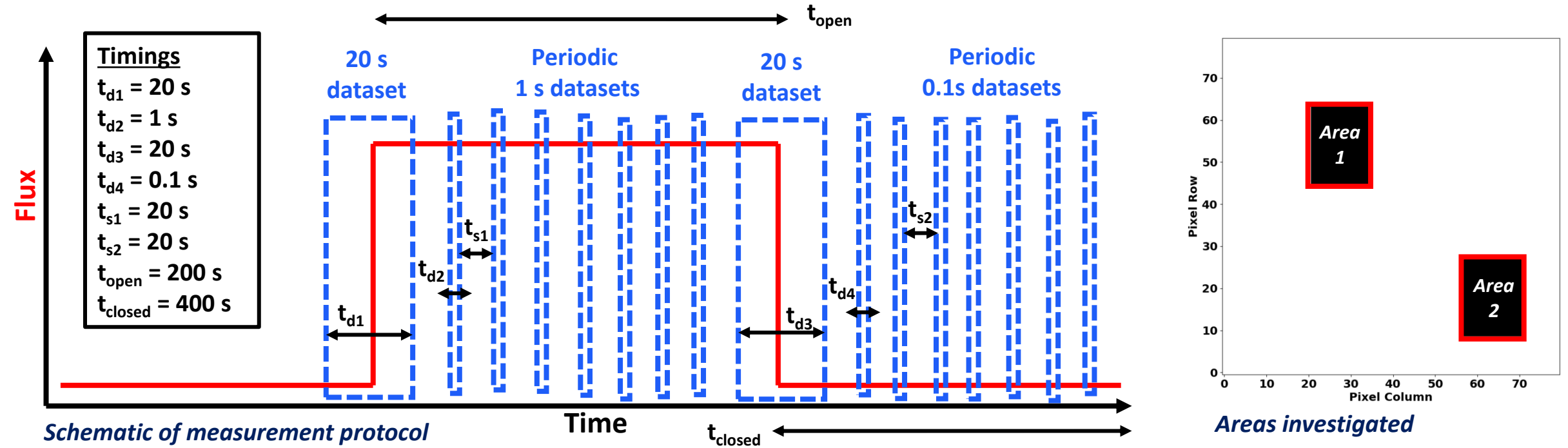
5 Next Steps

Future Work planned



Format of Dynamic Datasets

- Dynamic datasets taken under specific conditions to further characterise 'excess leakage current' effect



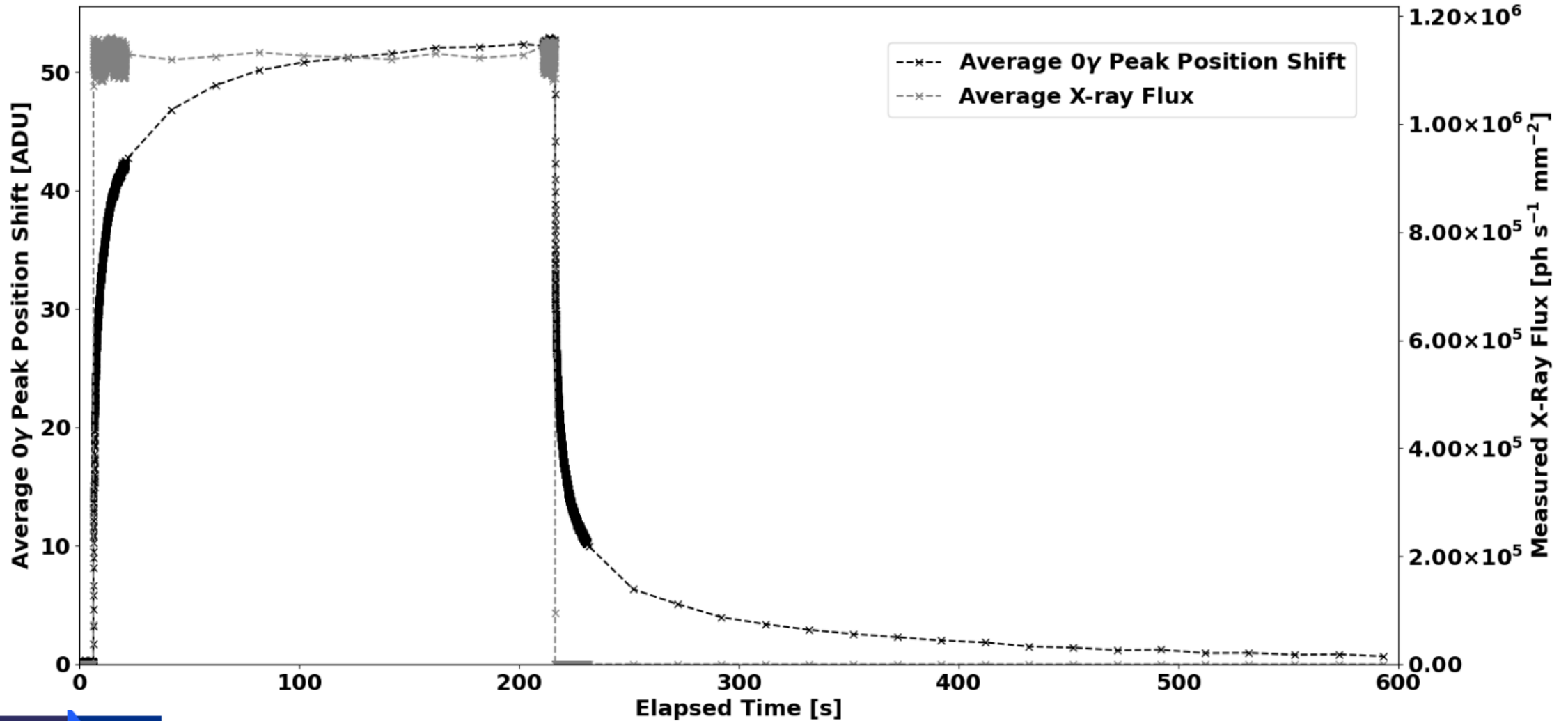
Variables investigated

Variable	Values
Energy (keV)	12, 20
Incident Flux ($10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$)	0.3, 1.2, 3.1, 7.8
Sensor Temperature ($^{\circ}\text{C}$)	2.5, 10, 20, 30, 40, 50
Sensor Bias Voltage (-V)	500, 750, 1000



Example Dataset Results

Parameter	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

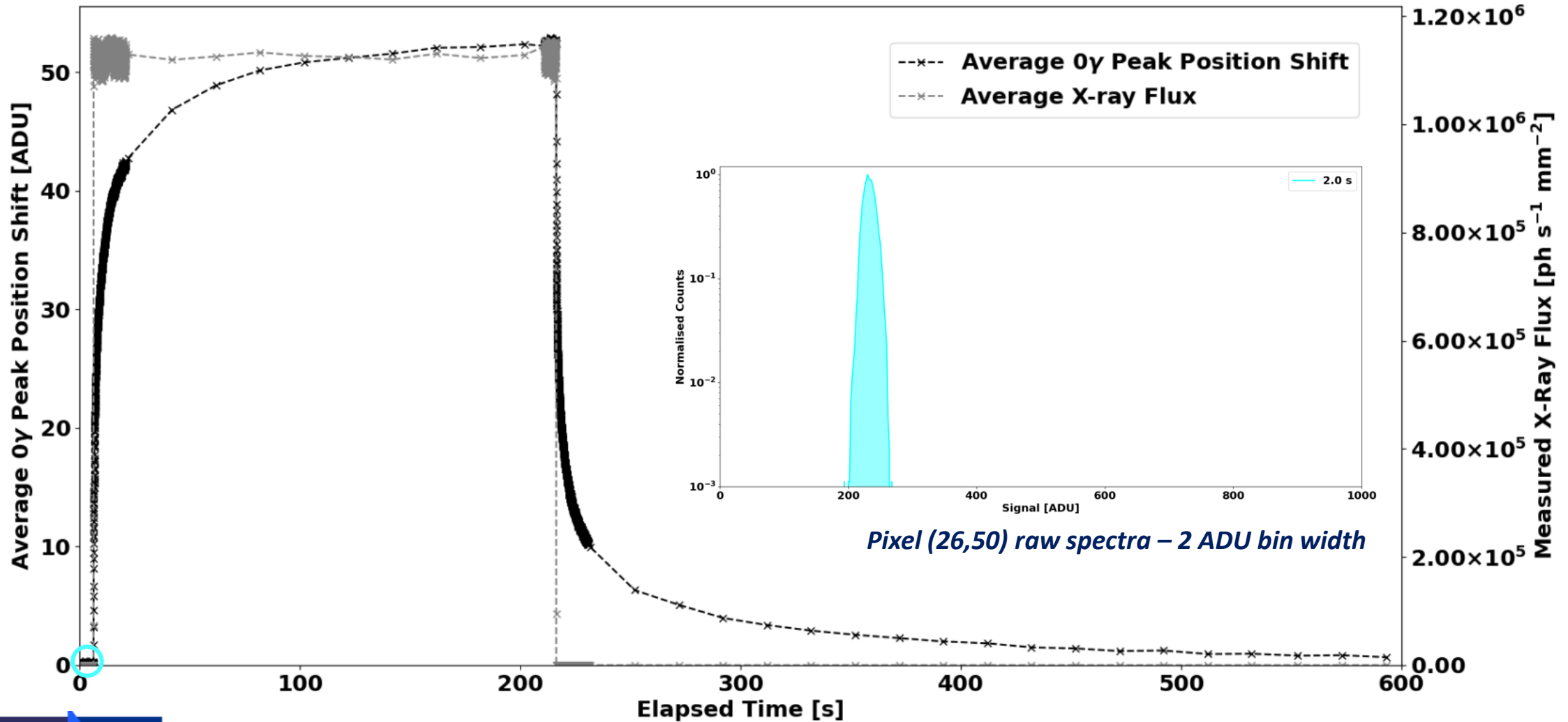


Science and
Technology
Facilities Council

Evolution of average 0γ peak shift and X-ray flux – 10⁴ frame sampling window

Example Dataset Results

Parameter	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

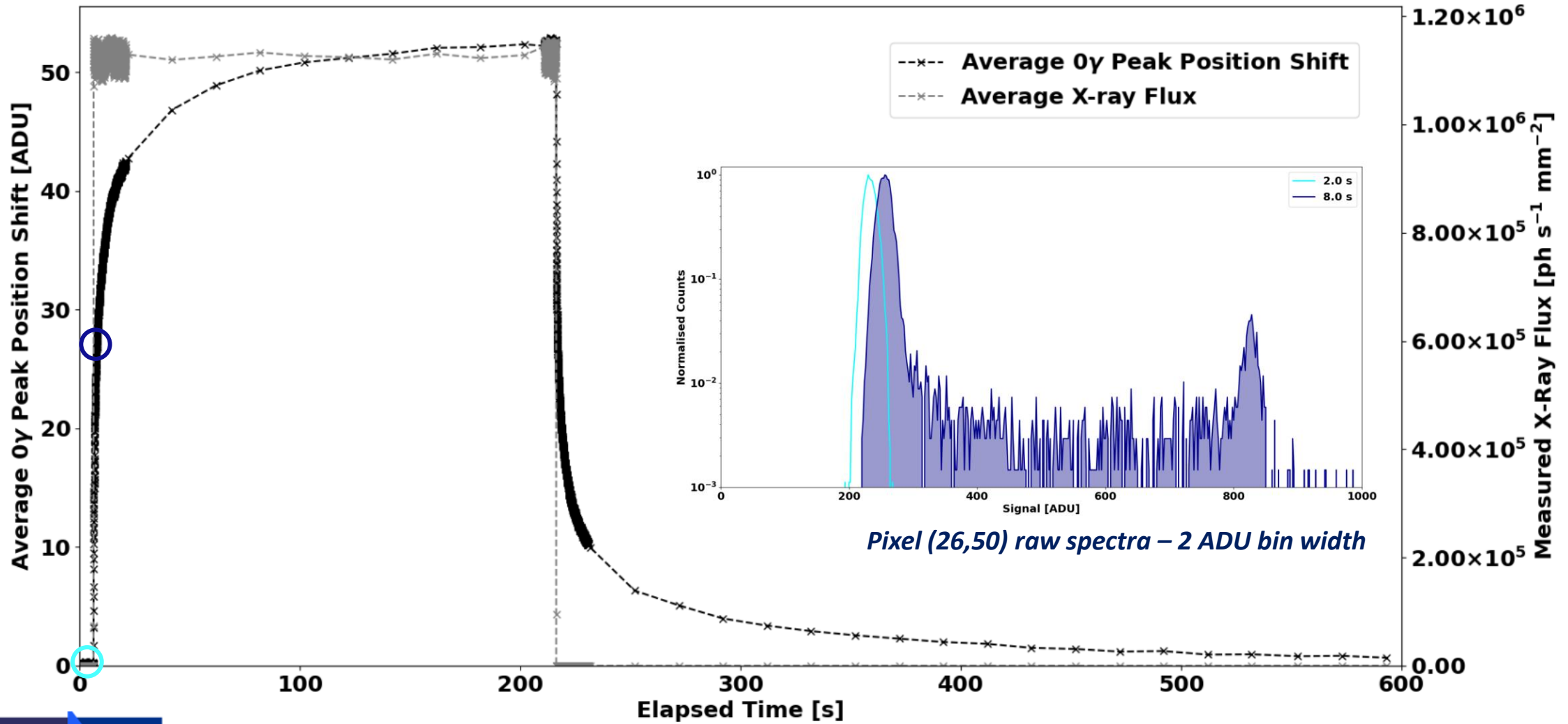


Evolution of average 0γ peak shift and X-ray flux – 10^4 frame sampling window



Example Dataset Results

Parameter	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

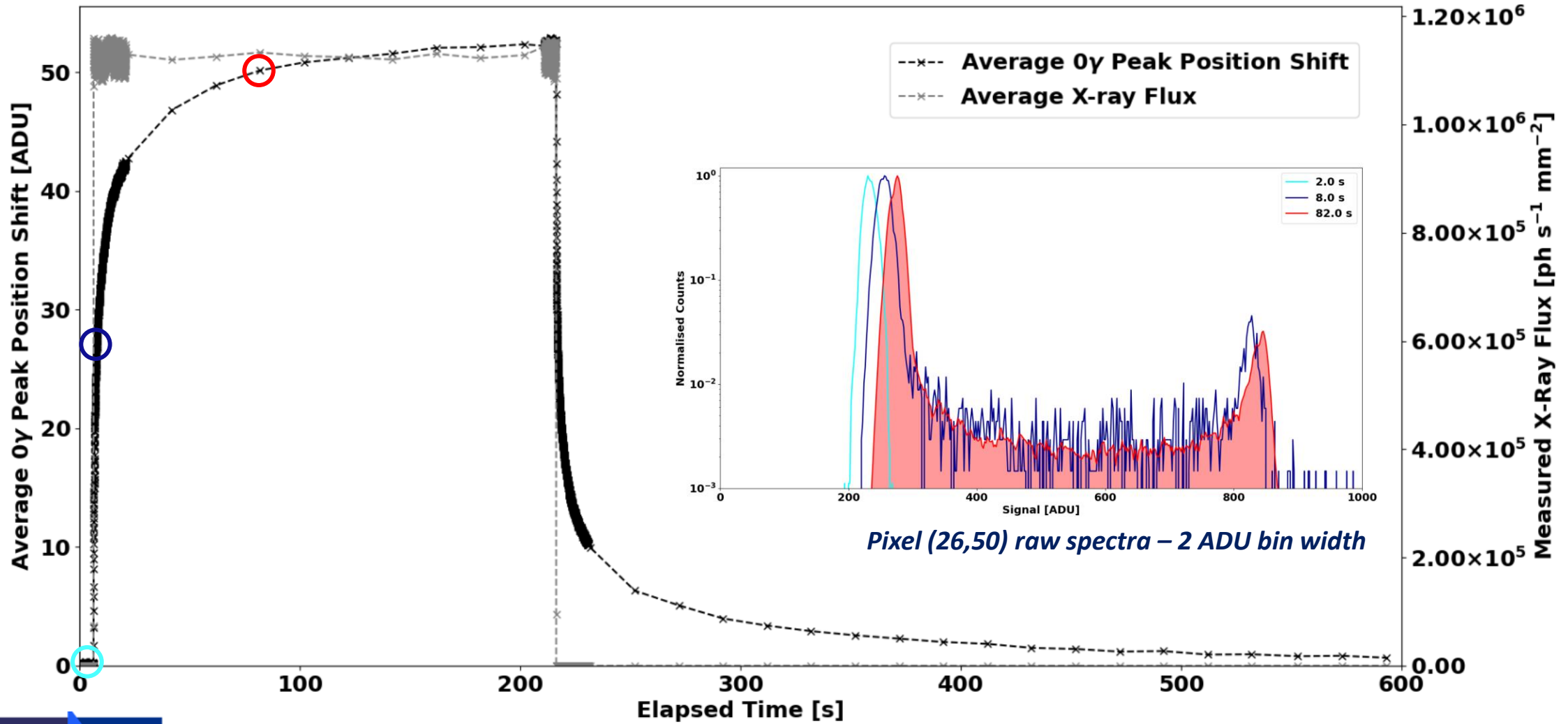


Evolution of average 0γ peak shift and X-ray flux – 10^4 frame sampling window



Example Dataset Results

Parameter	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

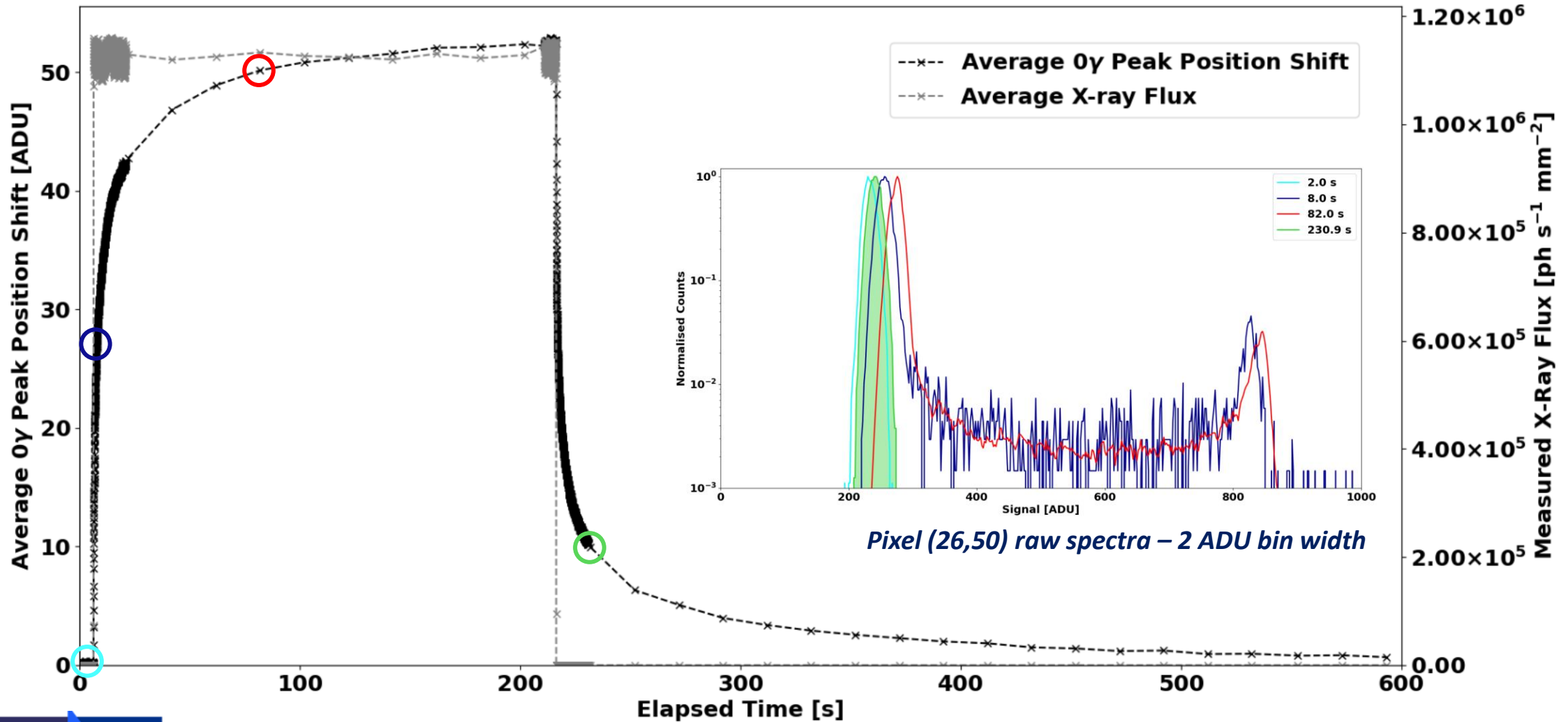


Evolution of average 0γ peak shift and X-ray flux – 10^4 frame sampling window



Example Dataset Results

Parameter	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

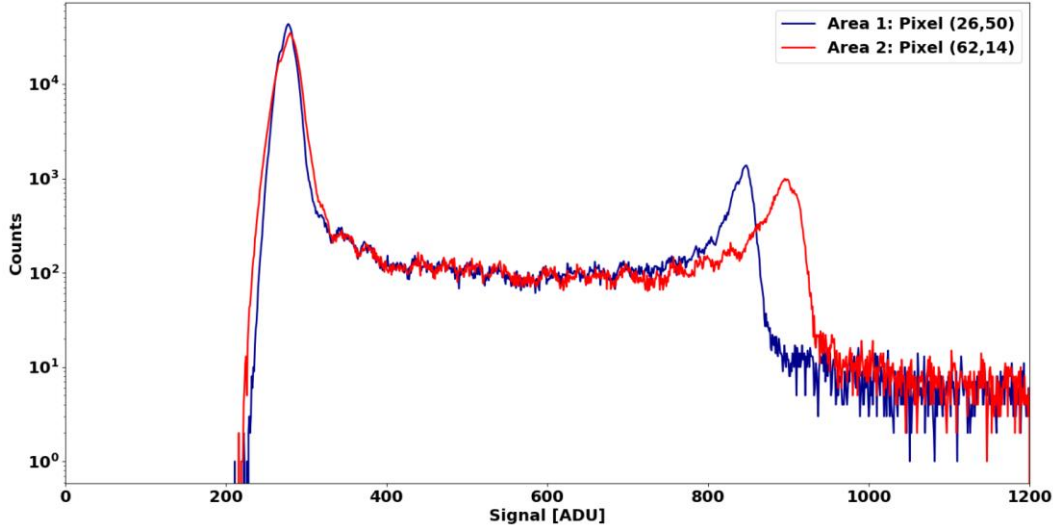


Evolution of average 0γ peak shift and X-ray flux – 10^4 frame sampling window

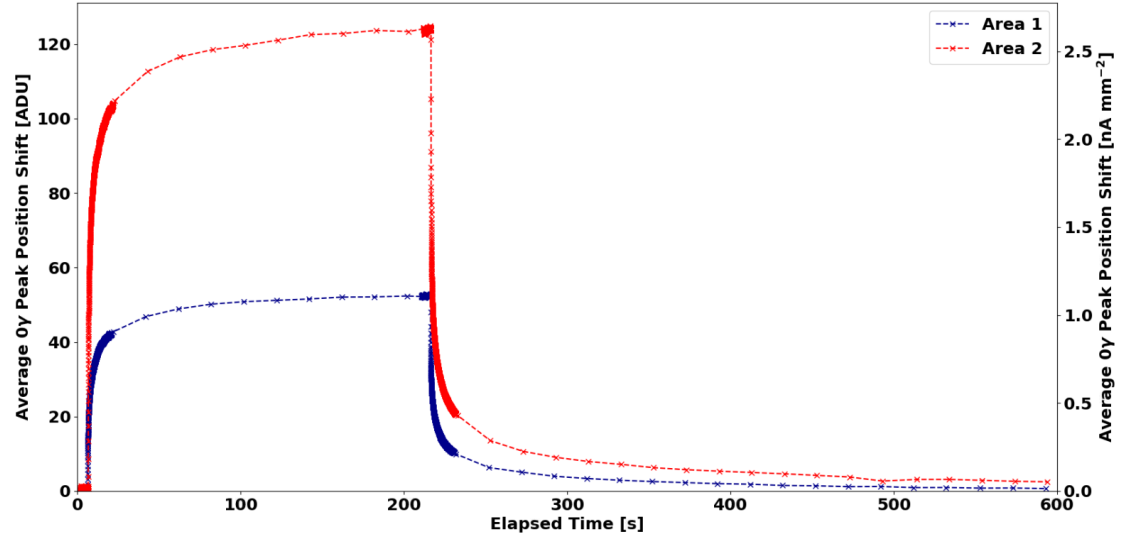


Spatial Dependency

Fixed Param	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V



Raw histograms at $t \approx 200 \text{ s}$ – 1 ADU bin width

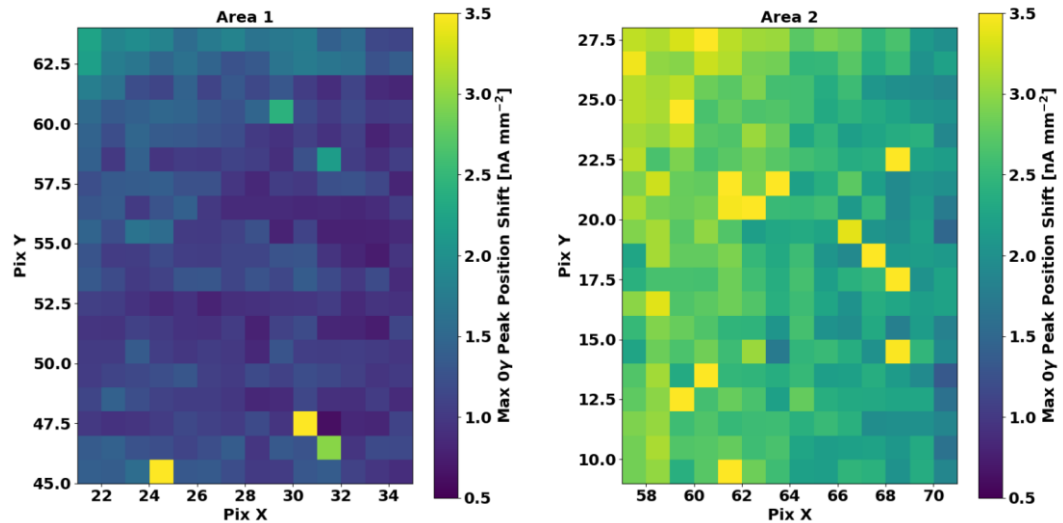


Average 0y peak position shift in the beam region

Average shifts in the ROI*

Area	Shift (ADU)	Shift (nA mm^{-2})
1	51 ± 17	1.1 ± 0.4
2	121 ± 21	2.4 ± 0.4

*250 ADU threshold limit used for statistics



Max 0y peak position shift in the ROI

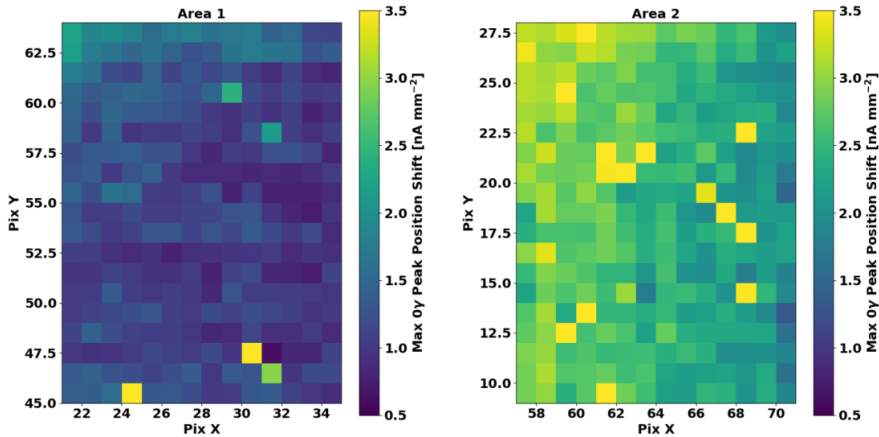


Science and
Technology
Facilities Council

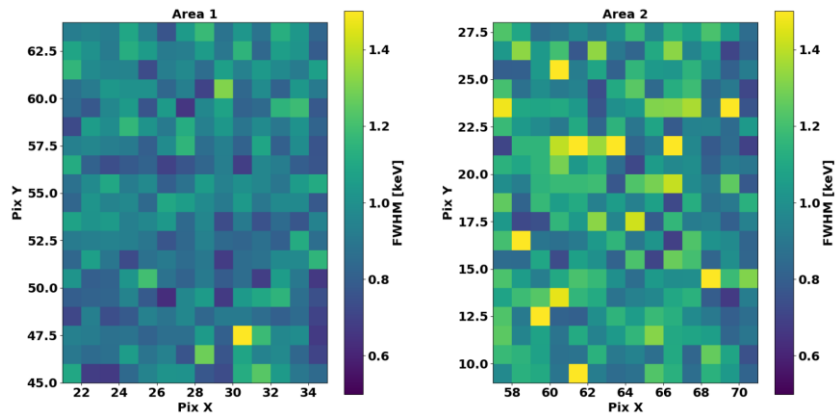
Spatial Dependency

Fixed Param	Energy	Gain	Flux	Temp	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	20 °C	-1000 V

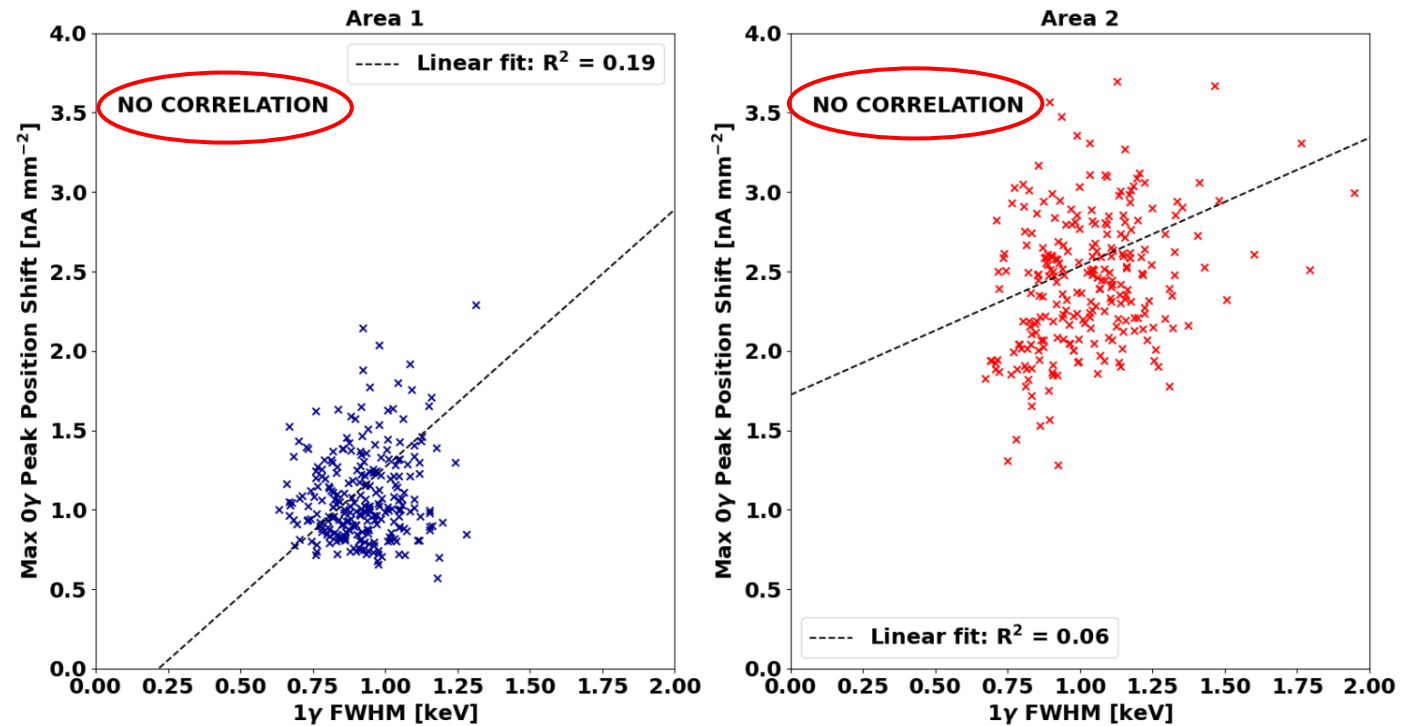
For comparison:



Max 0γ peak position shift in the ROI



1γ FWHM in the ROI



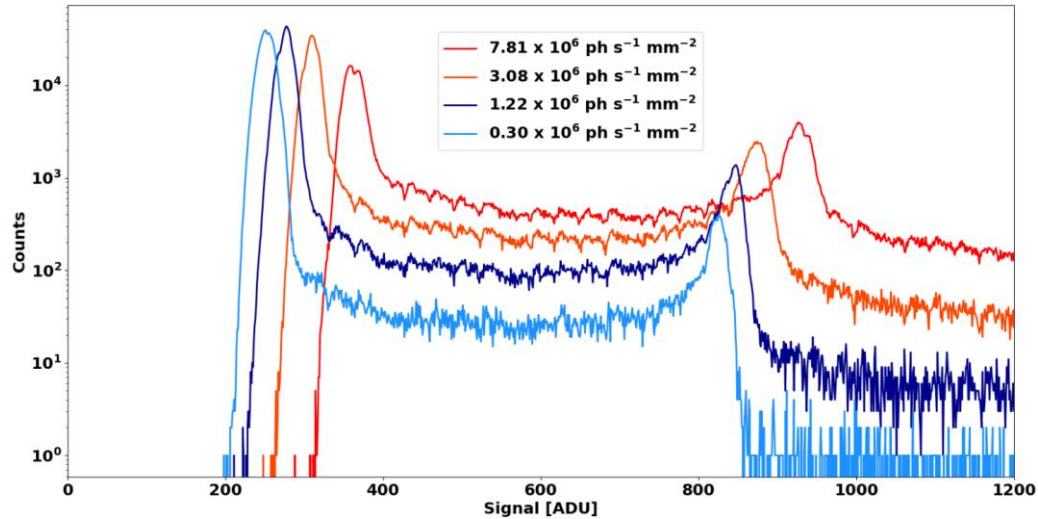
Mapping max 0γ peak shifts against the 1γ FWHM

- Photo peak **FWHM** dictated by bulk properties
- **No correlation** in fits of 0γ peak shifts against 1γ photo peak FWHM
 - Suggests **excess current** dictated by interface properties



Flux dependency

Fixed Param	Energy	Gain	Temp	Bias
Value	20 keV	High	20 °C	-1000 V

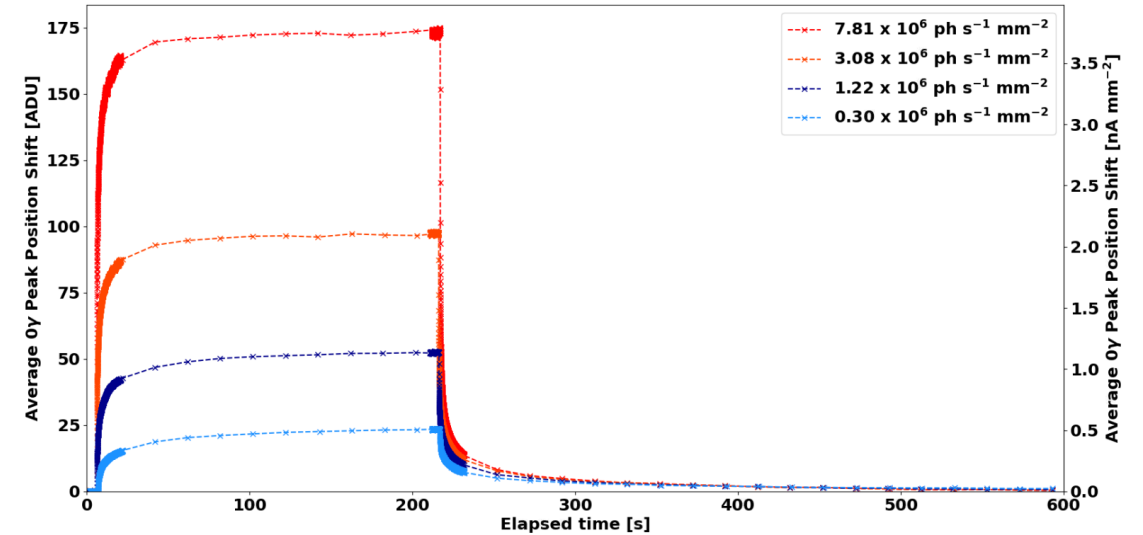


Pixel (26,50) raw histograms at $t \approx 200$ s – 1 ADU bin width

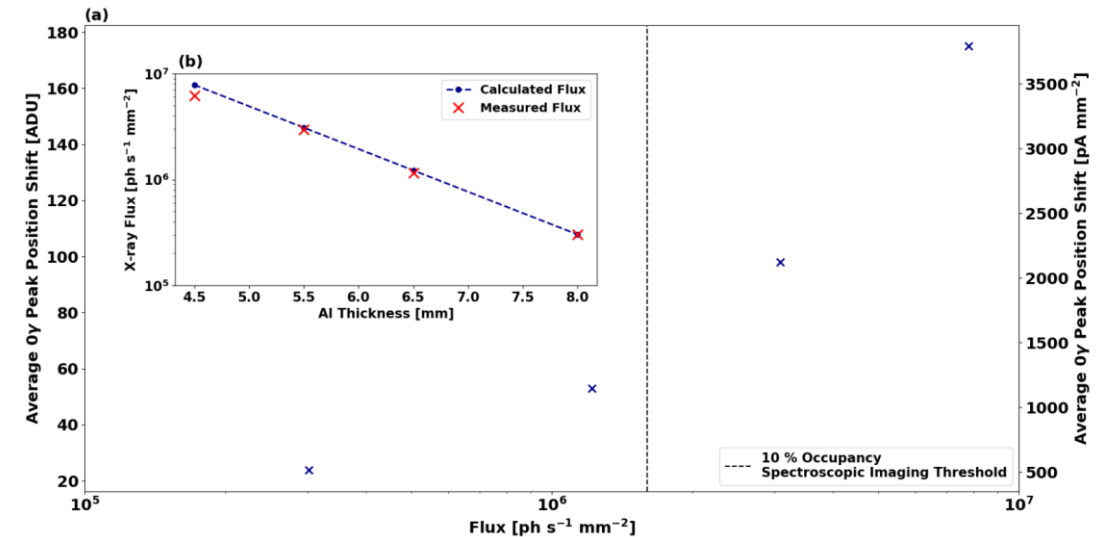
Average O_y peak position shift decay times

Flux (10^6 ph s^{-1} mm^{-2})	Decay time to 15 ADU (s)*
0.30	0.91
1.22	5.59
3.08	9.42
7.81	12.20

*15 ADU chosen as ~ 0.5 keV (\sim resolution of $HEXITEC_{MHz}$)



Average O_y peak shift in the beam

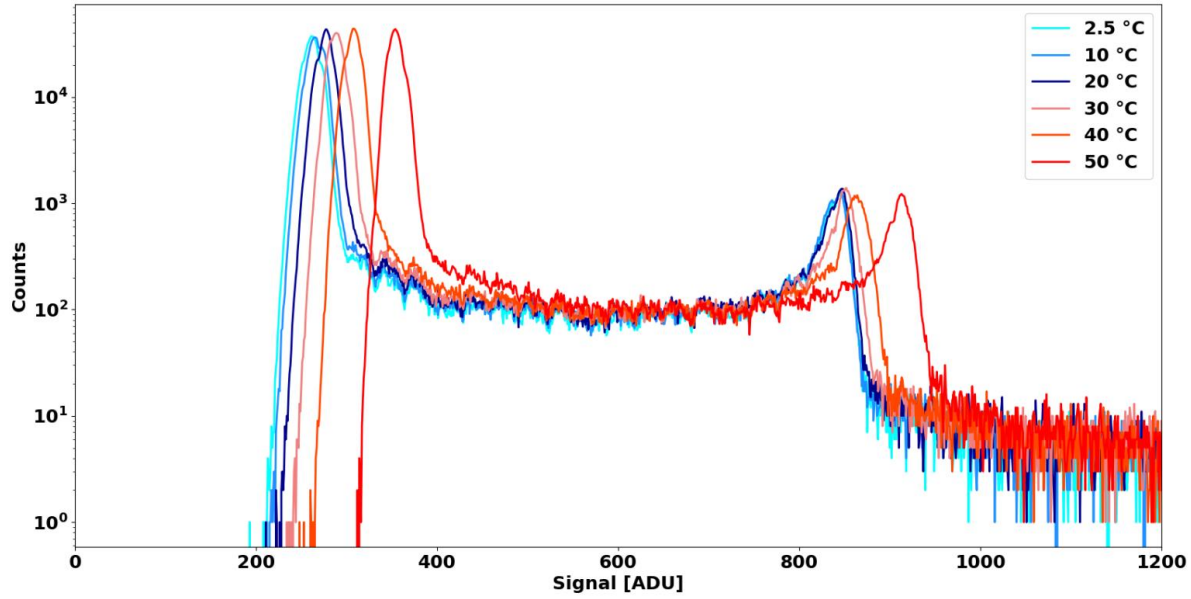


(a) O_y peak shift at calculated fluxes. (b) Comparison of calculated and measured fluxes

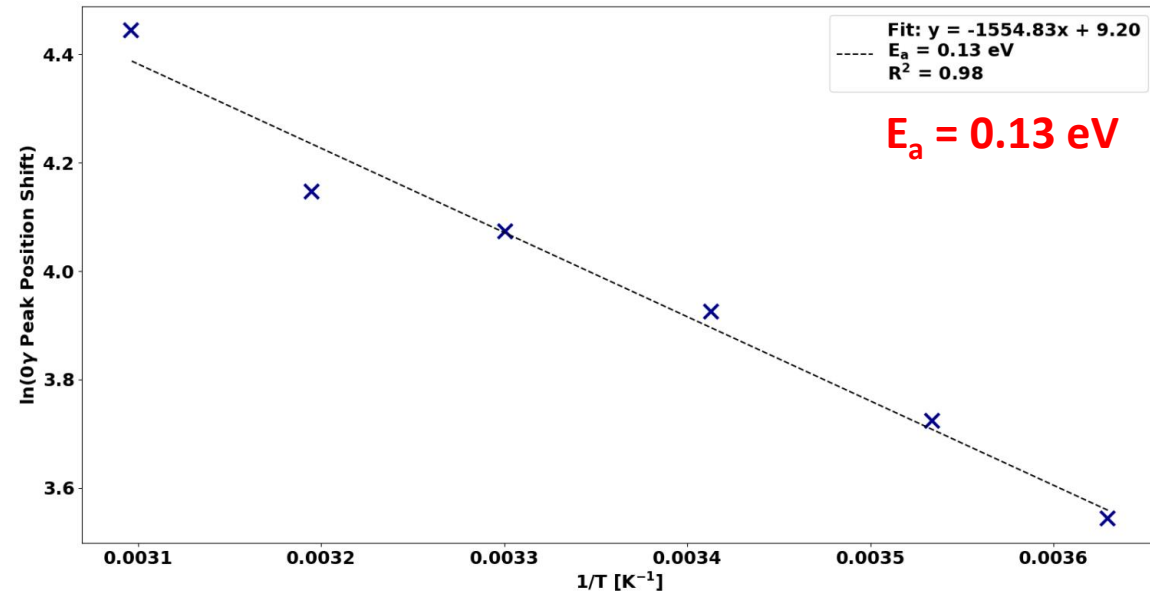


Temperature dependency

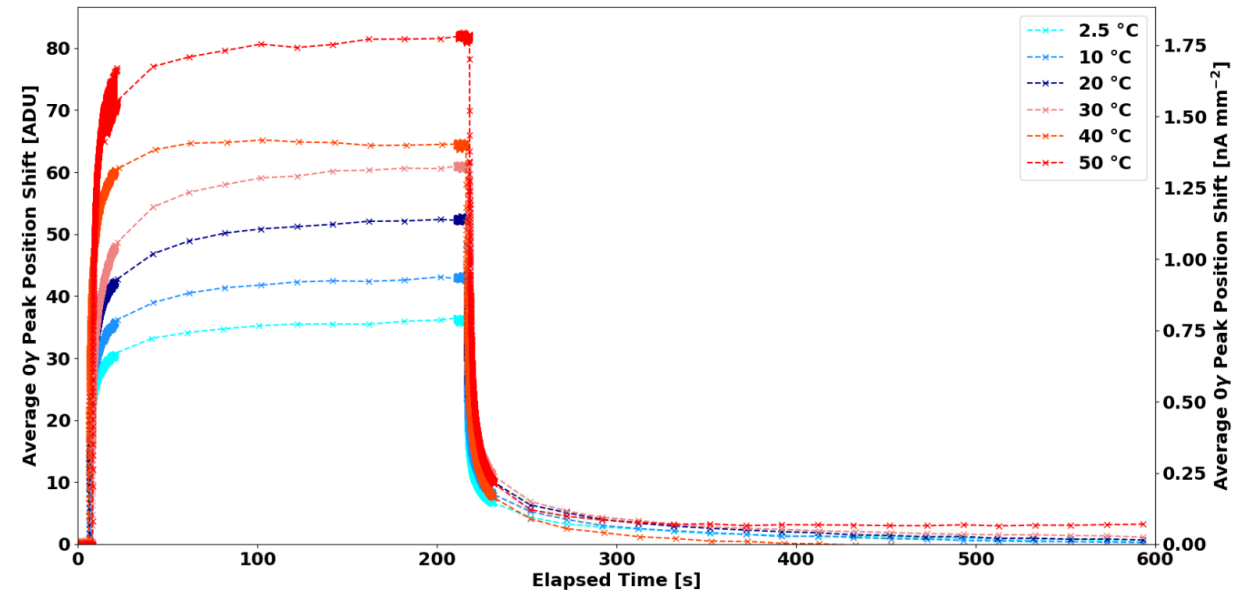
Fixed Param	Energy	Gain	Flux	Bias
Value	20 keV	High	$1.2 \times 10^6 \text{ ph s}^{-1} \text{ mm}^{-2}$	-1000 V



Pixel (26,50) raw histograms at $t \approx 200 \text{ s} - 1 \text{ ADU}$ bin width



Arrhenius
Analysis



Average Oy peak position shift in the beam

- **0.13 eV E_a** associated with well-known CZT defect
 - A-centres generated by Indium doping

Agenda

1 HEXITEC_{MHz} Overview

The next generation of HEXITEC systems

2 Redlen HF-CZT Overview

CdZnTe for use at high X-ray fluxes ($<10^9$ ph s⁻¹ mm⁻²)

3 Initial HF-CZT Test Results

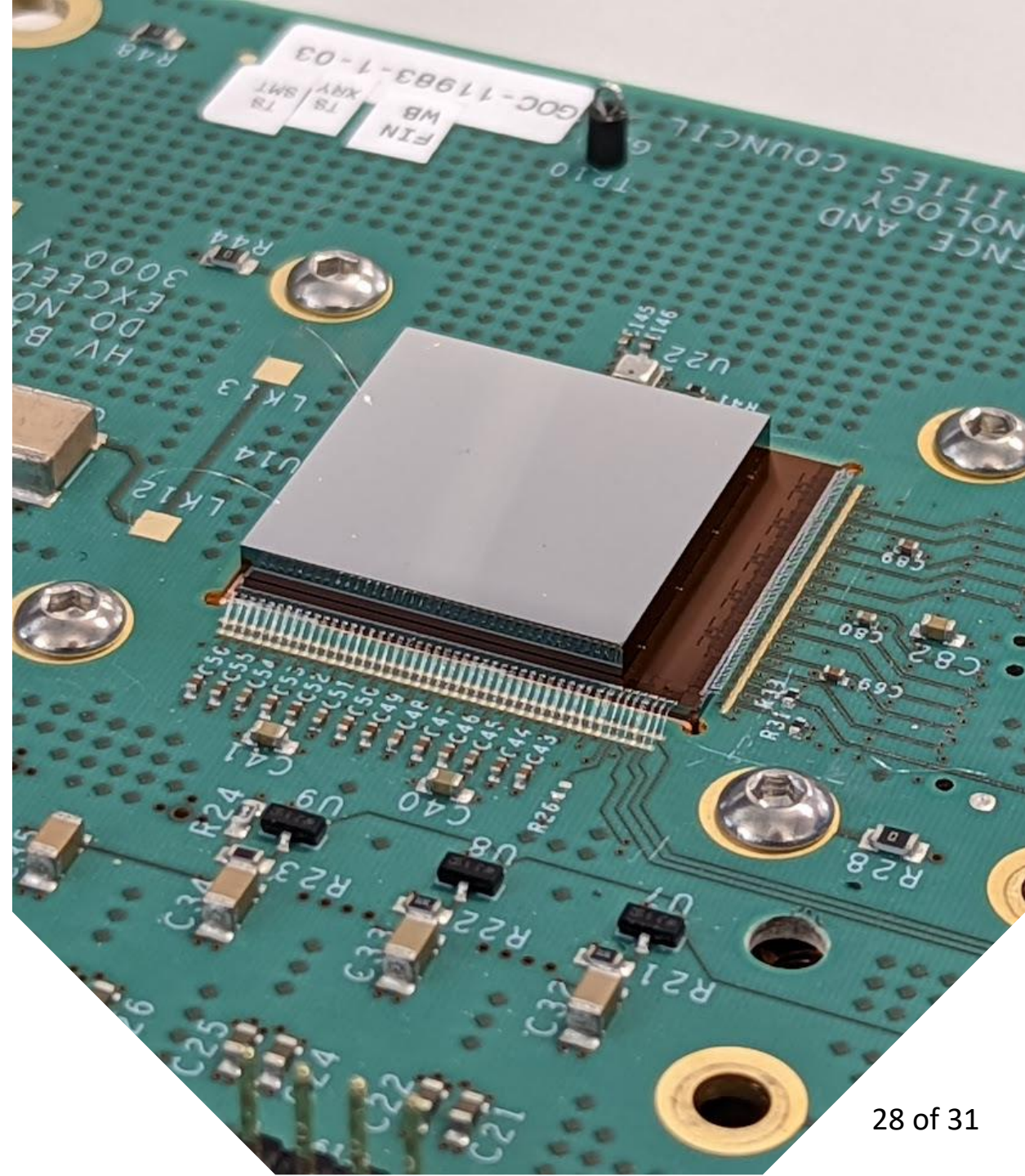
Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2022

4 Recent HF-CZT Test Results

Results from HF-CZT characterisation carried out at the DLS B16 Test Beamline in December 2023

5 Next Steps

Future Work planned



Next Steps

Testing and delivery of new DAQ system

- Verification of 80×80 output, in-FPGA dark-correction and histogramming
- Will enable lab-based analysis of effect using lower-flux sealed sources

ESRF beamtime (Jul 2024) ≤ 75 keV

- Temperature-dependency of 'excess leakage current' effect
 - Further Arrhenius analysis
 - PICTS analysis of HEXITEC_{MHz} data

DLS B16 beamtime (Dec 2024) ≤ 20 keV

- Novel HF-CZT HEXITEC-MHz detector variants
 - New low-temp hybridisation (<80 °C) method
 - Redlen sensors with new Ti-anode technology



The HEXITEC_{MHz} camera system

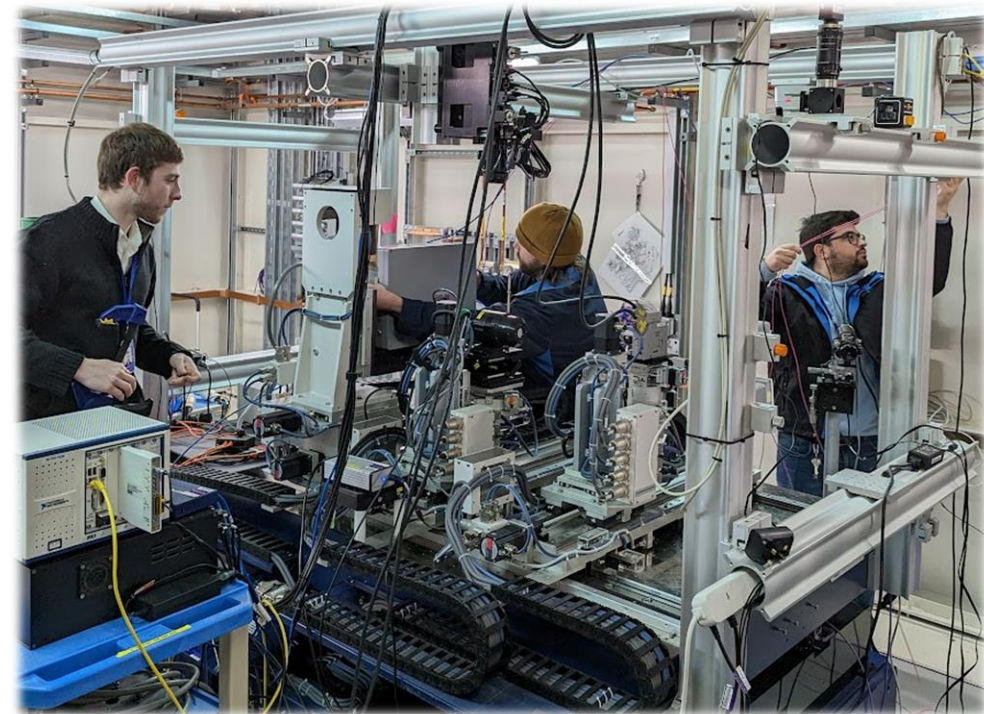
Summary

- Results revealed an ‘**excess leakage current**’ effect in **HF-CZT**
 - Not present in p-type Si results
- Arrhenius analysis suggests related to an **Indium-based CZT defect**
- Magnitude **dependent on incident X-ray flux**
 - Significant $>10^5 \text{ ph s}^{-1} \text{ mm}^{-2}$
 - **3.6 nA mm^{-2} at $7 \times 10^7 \text{ ph s}^{-1} \text{ mm}^{-2}$**
- At spectroscopic fluxes, lower excess currents measured.
 - **0.48 nA mm^{-2} at $3 \times 10^5 \text{ ph s}^{-1} \text{ mm}^{-2}$**
 - In-FPGA $\text{HEXITEC}_{\text{MHz}}$ firmware enables **real-time corrections**
- Further characterisation planned with $\text{HEXITEC}_{\text{MHz}}$
 - Validates detector’s capability for MHz materials characterisation

Please contact me with further questions: ben.cline@stfc.ac.uk



Science and
Technology
Facilities Council



Team members at DLS B16 Test Beamline

HEXITEC_{MHz}

Funded by the: Centre for Instrumentation (CFI) run by Marcus French

Detector Development

Ivan Church
Ben Cline
Matt Hart
Paul Seller
Dave Sole
Matt Wilson
Matt Veale

Interconnect

Paul Adkin
Paul Booker
Toby Brookes
Navid Ghorbanian
John Lipp
Andreas Schneider

Detector Systems Software

Dominic Banks
Adam Davies
Josh Harris
Tim Nicholls
Joseph Nobes

PCB Design Office

Darren Ballard
Dan Becket
Chris Day

Detector Systems

William Helsby

ASIC Design

Stephen Bell
Thomas Gardiner
Lawrence Jones
Mark Prydderch

Electronic Systems Design

Rob Halsall
Sooraj Pradeep
Matt Roberts



Science and
Technology
Facilities Council